

**PATENT ASSIGNMENT**

Electronic Version v1.1  
 Stylesheet Version v1.1

SUBMISSION TYPE:	NEW ASSIGNMENT
NATURE OF CONVEYANCE:	MERGER
EFFECTIVE DATE:	10/10/2003

**CONVEYING PARTY DATA**

Name	Execution Date
ASML US, INC.	10/10/2003

**RECEIVING PARTY DATA**

Name:	Thermal Acquisition Corp.
Street Address:	440 Kings Village Road
City:	Scotts Valley
State/Country:	CALIFORNIA
Postal Code:	95066-4081

**PROPERTY NUMBERS Total: 33**

Property Type	Number
Patent Number:	5059770
Patent Number:	6387764
Patent Number:	6206973
Patent Number:	5122391
Patent Number:	5088773
Patent Number:	5078922
Patent Number:	5786278
Patent Number:	5377300
Patent Number:	5855957
Patent Number:	5944900
Patent Number:	6352592
Patent Number:	5938851
Patent Number:	5976258
Patent Number:	6026589

**CH \$1320.00 5059770**

**PATENT**

Patent Number:	5849088
Patent Number:	4720395
Patent Number:	5626680
Patent Number:	4886954
Patent Number:	6005225
Patent Number:	4721427
Patent Number:	4721424
Patent Number:	4711989
Patent Number:	6300600
Patent Number:	6492621
Patent Number:	6462310
Patent Number:	7109131
Patent Number:	6465044
Patent Number:	6576060
Patent Number:	4993358
Patent Number:	6660391
Patent Number:	7029381
Patent Number:	6458013
Patent Number:	6874770

**CORRESPONDENCE DATA**

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ATTORNEY DOCKET NUMBER:	067538-TAC
NAME OF SUBMITTER:	Maria S. Swiatek

**Total Attachments: 62**

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## ASSIGNMENT OF PATENTS

This Assignment of Patents (this "Assignment") is effective as of the Initial Closing Date (as defined in the Asset Purchase Agreement (the "Asset Purchase Agreement"), dated as of October 10, 2003, by and among ASML Holding N.V., a Dutch company ("Parent"), ASML U.S., Inc., a Delaware corporation and a wholly-owned subsidiary of Parent ("Seller U.S."), and the other affiliates of Seller U.S. party thereto (together with all of the foregoing parties, each a "Seller" and collectively the "Sellers"), on the one hand, and Thermal Acquisition Corp., a Delaware corporation ("Buyer"). Capitalized terms used herein but not defined shall have the meanings ascribed to such terms in the Asset Purchase Agreement.

WHEREAS, upon the terms and subject to the conditions in the Asset Purchase Agreement, Sellers have agreed to assign and transfer to Buyer, among other things, certain Patents (as defined below);

WHEREAS, in order to further effect the assignment and transfer of such Patents, Buyer has requested that Seller U.S. execute and deliver to Buyer this Assignment;

NOW, THEREFORE, for good and valuable consideration, the receipt and sufficiency of which is hereby acknowledged:

1. Sellers agree to and hereby do assign, sell, transfer, grant and convey to Buyer, its successors and assigns, all of Sellers' worldwide right, title and interest in and to all Patents listed on schedule 3.18(a)(i) of the Disclosure Schedule and all causes of action, demands, judgments, claims, or other similar rights of Sellers relating primarily to such Patents.

"Patents" shall mean all U.S. and foreign patents and applications therefor and all reissues, divisions, renewals, extensions, provisionals, continuations and continuations-in-part thereof.

2. Sellers authorize and request the United States Patent and Trademark Office and head of any foreign patent office to issue all patent registrations which may issue on any applications for any Patents to Buyer, its successors and assigns, in accordance with this Assignment.

3. Promptly upon the request of Buyer, Sellers shall execute such documents and perform such actions as may be necessary to perfect the assignment of rights contained in this Assignment.

4. Nothing herein shall affect, or be deemed to affect, the representations, warranties, covenants, and indemnities contained in the Asset Purchase Agreement.

5. This Assignment may be executed in one or more counterparts and signature may be delivered by facsimile, each of which shall be deemed an original, but all of which together shall constitute one and the same instrument.

IN WITNESS WHEREOF, Seller U.S. has caused this instrument to be executed by its duly authorized corporate officer as of the Closing Date.

ASML U.S., Inc.

By: C. Douglas Marsh  
Name: C. Douglas Marsh  
Title: Vice President Business Integration  
& U.S. Institutional Relations

ACKNOWLEDGED AND AGREED:

Thermal Acquisition Corp., a Delaware Corporation

By: \_\_\_\_\_  
Name: Jerrold Curtini  
Title: President and Chief Executive Officer

IN WITNESS WHEREOF, Seller U.S. has caused this instrument to be executed by its  
duly authorized corporate officer as of the Closing Date.

ASML U.S., Inc.


By:

Name: C. Douglas Marsh  
Title: Vice President Business Integration  
& U.S. Institutional Relations

ACKNOWLEDGED AND AGREED:

Thermal Acquisition Corp., a Delaware Corporation

By:

  
Name: Jerauld Cutini  
Title: President and Chief Executive Officer

DISCLOSURE SCHEDULES

SCHEDULE 3.18(a)(1)

The following Patents:

SV387330.3



Attachment 1 to  
Disclosure Schedule 3.18(a)(1)

Reference No.	Inventors	Serial No./ Filing Date	Patent No./ Issue Date	Foreign Country
A 16178 6	AJT	07/068,727 06/29/87	4,845,054 07/04/89	
FA 16178 6-JP	AJT	61-137340 06/14/86	2134184 12/26/97	Japan
A 16178 7	AJT	07/044,326 10/27/87	4,834,022 05/30/89	
FA 16178 7-JP	AJT	61-165449 07/14/86	2076448 08/09/96	Japan
A 16178 8	AJT	707262 03/01/85	4,673,799 06/16/87	
A 40356	AJT	Closed		
A 44048	AJT	07/128,806 12/04/87	4,834,020 05/30/89	
FA 44048 JP	AJT	63-307653 12/05/88	2930960 05/21/99	Japan
FA 44048 E.K	AJT	Closed		
A 44153	AJT	07/089,591 08/26/87	4,787,813, 11/29/88	Expired
A 44521	AJT	06/907,503 09/15/86	Abandoned	
A 44521 1	AJT	07/214,909 06/29/88	4,891,247 01/02/90	Abandoned

I-71935/MESS (463035-828)  
1089128

10/8/2005

Reference No.	Title/Inventors		Serial No./ Publ. Date	Patent No./ Issue Date	Foreign Countries	
EA 44521	1-JP	AJT	BOROSILICATE GLASS FILMS FOR MULTILEVEL METALLIZATION STRUCTURES IN SEMICONDUCTOR DEVICES AND METHOD FOR IMPROVING THE STEP COVERAGE OF DIELECTRIC IN VLSI CIRCUITS	62-231991 09/16/87	Abandoned	Japan
EA 47444	1-EP	AJT	CHEMICAL VAPOR DEPOSITION USING DYSILANE/SILANE/Gralenski	Closed		Europe
EA 47444	DE	AJT MSS	CHEMICAL VAPOR DEPOSITION USING DYSILANE/Gralenski	07/23/82 08/31/88	Abandoned in favor of 07798,829 (A-47444-1)	Germany
EA 47444	KR	AJT MSS	CHEMICAL VAPOR DEPOSITION USING DYSILANE/Gralenski	P392E765.3 08/31/89	Abandoned	South Korea
EA 47444	JP	AJT MSS	CHEMICAL VAPOR DEPOSITION USING DYSILANE/Gralenski	1247289 08/31/89	Abandoned	Japan
EA 47444	GB	AJT MSS	PROCESSES USING DYSILANE/Gralenski	01-226366 08/31/89	Abandoned	United Kingdom
EA 47444	EP	AJT MSS	CHEMICAL VAPOR DEPOSITION USING DYSILANE/SILANE/Gralenski	8919291.8 08/24/89	Abandoned	Europe
EA 47444	PC	AJT MSS	CHEMICAL VAPOR DEPOSITION USING DYSILANE/SILANE/Gralenski	Closed		PCI
EA 47444	1	AJT MSS	CHEMICAL VAPOR DEPOSITION USING DYSILANE/Gralenski	07798,829 11/22/91	Abandoned in favor of 07991,500 (A-47444-2)	
EA 47444	2	AJT MSS	CHEMICAL VAPOR DEPOSITION USING DYSILANE/Gralenski	07991,500 12/1/92	Abandoned in favor of 08329,772 (A-47444-3)	
EA 47444	3	AJT MSS	CHEMICAL VAPOR DEPOSITION USING DYSILANE/Gralenski	08329,772 10/27/94	Abandoned per client ltr 09/14/98	
EA 52353		AJT	ELECTRICALLY INSULATED PIPE COUPLING APPARATUS/Gralenski	07570,122 08/17/90	5,988,773 02/18/92	
EA 52354		AJT WSG	INJECTOR AND METHOD FOR DELIVERING GASEOUS CHEMICALS TO A SURFACE/Bartholomew	07543,243 06/21/90	5,136,975 08/11/92	
EA 52354		AJT	SELF-CLEANING ORIFICE/Kambien	07513,807	5,113,789	

1-71935/MSS (46005-828)  
1059128

Reference No.	Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
	WSG	AJT			
FA 52354	KK	WSG	04/2/89	05/19/92	
FA 52354	JP	WSG	14/08/90	188614	South Korea
FA 52354	TW	AJT	09/18/90	01/13/99	Japan
FE 52354	DE	WSG	2-216935	29/3/90	
FE 52354	DE	AJT	08/17/90	09/03/99	Taiwan
FE 52354	ES	WSG	79106834	51810	
FE 52354	FR	AJT	08/15/90	02/14/92	Germany
FE 52354	FR	WSG	90307398.9	69017008	
FE 52354	FR	AJT	07/06/90	02/15/95	Spain
FE 52354	FR	WSG	90307398.9	453679	France
FE 52354	GB	AJT	07/06/90	Abandoned	
FE 52354	GB	WSG	90307398.9	02/15/95	United Kingdom
FE 52354	GR	AJT	07/06/90	453679	
FE 52354	GR	WSG	90307398.9	02/15/95	Greece
FE 52354	IT	AJT	90307398.9	Abandoned	
FE 52354	IT	WSG	07/06/90	453679	Italy
FE 52354	BE	AJT	07/06/90	02/15/95	
FE 52354	BE	WSG	90307398.9	453679	Belgium
FE 52354	CH	AJT	07/06/90	Abandoned	
FE 52354	CH	WSG	90307398.9	453679	Switzerland
FE 52354	EP	AJT	07/06/90	02/15/95	
FE 52354	EP	WSG	90307398.9	Abandoned	
FE 52354	LU	AJT	07/06/90	453679	Europe
FE 52354	LU	WSG	90307398.9	02/15/95	Luxembourg
FE 52354	NL	AJT	07/06/90	Abandoned	
FE 52354	NL	WSG	90307398.9	453679	Netherlands
FE 52354	SE	AJT	07/06/90	02/15/95	
FE 52354	SE	WSG	90307398.9	453679	Sweden

F-71935/MSS (463035-828)  
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Reference No.		Applicant	Serial No./ Filing Date	Foreign No./ Issue Date	Foreign Countries
FE 52354	DK	AJT WSG	94307398.9 07/06/90	Abandoned 453679 02/15/95 Abandoned	Denmark
FE 52354	AT	AJT	90307398.9 07/06/90	453679 02/15/95 Abandoned	Austria
A 53835		AJT JEM	07/601,261 10/22/90	Abandoned 08/19/92	
FA 53835	KR	AJT	18591/91 10/22/91	Abandoned 08/19/92	South Korea
FA 53835	JP	AJT	3-274072 10/22/91	Abandoned 08/19/92	Japan
FE 53835	EP	AJT	91309735.8 10/22/91	Abandoned	Europe
A 53836		AJT	07/601,270 10/22/90	5,078,922 01/07/92	
FA 53836	JP	AJT	3-274069 10/22/91	1929857 05/12/95	Japan
FA 53836	KR	AJT MSS	18592/91 10/22/91	191851 01/27/99	South Korea
FE 53836	EP	AJT	91309736.6 10/22/91	Abandoned	Europe
A 53837		AJT	Closed		
A 53859		AJT			
FA 53859	JP	AJT	07/601,408 10/23/90	5,029,471 07/09/91	
FA 53859	KR	AJT MSS	3-275317 10/23/91	1903072 02/08/95	Japan
FE 53859	EP	AJT	18633-91 10/23/91	216658 06/01/99	South Korea
			91309743.2 10/22/91	Abandoned	Europe

I-7195/MSS (463035-828)  
10591DE

Reference No.	Title/Inventors	Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
A 51860	VAPOR DELIVERY SYSTEM AJT	Closed		
A 53861	CHEMICAL REFILL SYSTEM AJT	Closed		
A 56598	HEATER FOR PROCESSING GASES/Collins AJT	07/971,490 11/04/92	5,377,300 12/27/94	
FA 56598 JP	GAS HEATER FOR PROCESSING GASES/Collins AJT	6-511396 11/03/93	Abandoned	Japan
FA 56598 KR	GAS HEATER FOR PROCESSING GASES/Collins AJT	701790/95 11/03/93	163246 09/04/98	South Korea
FE 56598 EP	GAS HEATER FOR PROCESSING GASES/Collins AJT	94900500.3 11/03/93	0666972 01/07/99	Europe
FE 56598 HK	GAS HEATER FOR PROCESSING GASES/Collins AJT	98114622.0 12/22/98	1014206B 06/16/00	Hong Kong
FE 56598 DE	GAS HEATER FOR PROCESSING GASES/Collins AJT	94900500.3 11/03/93	Abandoned P69322975 01/07/99	Germany
FE 56598 FR	GAS HEATER FOR PROCESSING GASES/Collins AJT	94900500.3 11/03/93	0666972 01/07/99	France
FE 56598 GB	GAS HEATER FOR PROCESSING GASES/Collins AJT	94900500.3 11/03/93	0666972 01/07/99	Great Britain
FE 56598 IT	GAS HEATER FOR PROCESSING GASES/Collins AJT	94900500.3 11/03/93	0666972 01/07/99	Italy
FP 56598 PC	GAS HEATER FOR PROCESSING GASES/Collins AJT	PCT/US93/10532 11/03/93	Closed	PCT
A 57727	BP&G STABILITY ENHANCING CAP LAYER/ Engelhardt	Closed		
A 57728	OZONE PRETREATMENT FOR EMERGVED VIA RESISTANCE/Curtis	Closed		
A 58019	CHEMICAL VAPOR DEPOSITION OF SILICON DIOXIDE USING HEXAMETHYLDISILAZANE/Krusell	08/071,516 06/03/93	5,304,398 04/19/94	
FP 58019 PC	CHEMICAL VAPOR DEPOSITION OF SILICON DIOXIDE FROM HEXAMETHYLDISILAZANE AND OZONE/OXYGEN/Krusell		Abandoned	PCT

L-71935/MS (463035-828)  
1059128

Reference No.	Classification	Title/Inventors	Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
A	AJI	A THIN FILM SEMICONDUCTOR DEVICE AND METHOD/Harada	08/191,091	Abandoned	
FP	AJT	A THIN FILM SEMICONDUCTOR DEVICE AND METHOD/Harada	02/03/94	Abandoned	
A	AJT	METHOD OF MANUFACTURING A GLASS SUBSTRATE FOR A THIN FILM/Harada	PC70US94/01352 02/04/94	Abandoned	FCT
FP	AJT	METHOD OF MANUFACTURING A GLASS SUBSTRATE FOR A THIN FILM/Harada	08/191,093 02/03/94	Abandoned in favor of FWC 08/542,279 (A-59072-1)	
A	AJT	METHOD OF MANUFACTURING A GLASS SUBSTRATE FOR A THIN FILM/Harada	PC70US94/01278 02/04/94	Abandoned	FCT
A	AJT	METHOD OF MANUFACTURING SIDE WALLS AND SEMICONDUCTOR DEVICE HAVING SIDE WALLS/Harada, Hattori	08/542,279 10/12/93	Abandoned	
FP	AJT	METHOD OF MANUFACTURING SIDE WALLS AND SEMICONDUCTOR WITH SIDE WALLS/Harada, Hattori	08/237,691 05/04/94	Abandoned in favor of FWC 08/512,346 (A-59073-1)	
A	AJT	METHOD OF MANUFACTURING SIDE WALLS AND SEMICONDUCTOR WITH SIDE WALLS/Harada, Hattori	PC70US94/05315 05/13/94	Abandoned	FCT
A	AJT	METHOD OF MANUFACTURING SIDE WALLS AND SEMICONDUCTOR DEVICE HAVING SIDE WALLS/Harada, Hattori	08/512,346/ 08/08/95	Abandoned	
A	AJT	TRITHOXY-SILANE (TRIS) AS A PRECURSOR FOR THE DEPOSITION OF SiO <sub>2</sub> /Schmidt	FWC of 08/237,691 Filed 05/04/94	Abandoned	
A	AJT	SINGLE BODY INJECTOR AND METHOD FOR DELIVERING GASES TO A SURFACE/Dedontney	Closed		
EA	AJT	SINGLE BODY INJECTOR FOR DELIVERING GASES TO A SURFACE/Dedontney	08/276,815 07/18/94	Abandoned in favor of FWC 08/621,772 (A-59471-1)	
EA	AJT	SINGLE BODY INJECTOR FOR DELIVERING GASES TO A SURFACE/Dedontney	7-181702 07/18/95	2790437 06/12/98	Japan
EA	AJT	SINGLE BODY INJECTOR FOR DELIVERING GASES TO A SURFACE/Dedontney	20936795 07/18/95	190355 01/20/99	South Korea
EA	AJT	SINGLE BODY INJECTOR FOR DELIVERING GASES TO A SURFACE/Dedontney	84100288 01/13/95	106107	Taiwan
FB	AJT	SINGLE BODY INJECTOR FOR DELIVERING GASES TO A SURFACE/Dedontney	95304783 A 07/10/95	12/29/99 P69513108.4 11/03/99	Germany

I-71935/MSS (4/3/03-828)  
1059128

Reference No.		Title/Inventors		Best Pat No./ Filing Date	Substant No./ Issue Date	Foreign Countries
FE	59471	EP	SINGLE BODY INJECTOR FOR DELIVERING GASES TO A SURFACE/Dodanmy	95304783.4 07/10/95	0697376 11/03/99	Europe
FE	59471	FR	SINGLE BODY INJECTOR FOR DELIVERING GASES TO A SURFACE/Dodanmy	95304783.4 07/10/95	0697376 11/03/99	France
FE	59471	GB	SINGLE BODY INJECTOR FOR DELIVERING GASES TO A SURFACE/Dodanmy	95304783.4 07/10/95	0697376 11/03/99	Great Britain
FE	59471	HK	SINGLE BODY INJECTOR	98111870.5 11/09/98	1011010B 06/16/00	Hong Kong
FE	59471	IT	SINGLE BODY INJECTOR FOR DELIVERING GASES TO A SURFACE/Dodanmy	95304783.4 07/10/95	0697376 11/03/99	Italy
FE	59471	NL	SINGLE BODY INJECTOR FOR DELIVERING GASES TO A SURFACE/Dodanmy	95304783.4 07/10/95	0697376 11/03/99	Netherlands
A	59471	1	SINGLE BODY INJECTOR AND METHOD FOR DELIVERING GASES TO A SURFACE/Dodanmy, Gradenski, Miller	08/621,772 03/22/96 FWC of 08/276,815 Filed 07/18/94	5,683,516 11/04/97	
A	59471	2	METHOD OF MANUFACTURING AN INJECTOR FOR CHEMICAL VAPOR DEPOSITION PROCESSING/Dodanmy, Gradenski, Miller	08/869,085 08/04/97 Div. of 08/276,815 Filed 07/18/94	5,935,647 08/10/99	
A	59471	3	SINGLE BODY INJECTOR FOR DELIVERING GASES TO A SURFACE/Miller, Dobkin	08/892,469 07/14/97 CIP of 08/621,772; which is an FWC of 08/276,815	6,022,414 02/08/00	
PA	59471	3-TW	SINGLE BODY INJECTOR FOR DELIVERING GASES TO A SURFACE/Miller, Dobkin	87111447 07/14/98	12A167 04/24/01	Taiwan
A	59471	4	SINGLE BODY INJECTOR AND DEPOSITION CHAMBER/Miller, Dobkin	09/113,823 07/10/98 CIP of 08/892,469; which is a CIP of 08/621,772; which is an FWC of	6,200,389 03/13/01	

I-71935/MSS (463035-828)  
1059128

Reference No.	Title/Inventors	Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
FP	SINGLE BODY INJECTOR AND DEPOSITION CHAMBER/Miller, et al.	08276,815	Closed	JCF
FA	SINGLE BODY INJECTOR AND DEPOSITION CHAMBER/Miller, et al.	PCIUS98/14393 07/10/98		China
FA	SINGLE BODY INJECTOR AND DEPOSITION CHAMBER/Miller, et al.	98807203.3 07/10/98		
FA	SINGLE BODY INJECTOR AND DEPOSITION CHAMBER, Adam Q. Miller, Daniel M. Dobkin	00108287.5		
FA	SINGLE BODY INJECTOR AND DEPOSITION CHAMBER/Miller, et al.	122100		Japan
FA	SINGLE BODY INJECTOR AND DEPOSITION CHAMBER/Miller, et al.	2000-503260 07/10/98		
FA	SINGLE BODY INJECTOR AND DEPOSITION CHAMBER/Miller, et al.	2000-7000430 07/10/98	355058 09/29/02	South Korea
FE	SINGLE BODY INJECTOR AND DEPOSITION CHAMBER/Miller, et al.	9906104-6 07/10/98	69697 03/04/02	Singapore
A	SINGLE BODY INJECTOR AND DEPOSITION CHAMBER/Miller, et al.	9893329.9 07/10/98		Europe
A	SINGLE BODY INJECTOR AND DEPOSITION CHAMBER/Miller, Dobkin	09757,542 01/09/01	6,521,048 02/18/03	
FA	METHOD OF FORMING A PLANAR LAYER OF MATERIAL/Pry, Lightfoot, Lomond	Divisional of 09/115,823 07/10/98		South Korea
FA	METHOD OF PLANARIZING A LAYER OF MATERIAL/Pry, Lightfoot, Lomond	08447,809 05/23/95	5,668,063 09/16/97	
FA	METHOD OF PLANARIZING A LAYER OF MATERIAL/Pry, Lightfoot, Lomond	70826997 05/06/96		Japan
FE	METHOD OF PLANARIZING A LAYER OF MATERIAL/Pry, Lightfoot, Lomond	8-535689 05/06/96		Europe
FP	METHOD OF PLANARIZING A LAYER OF MATERIAL/Pry, Lightfoot, Lomond	96914583.3 05/06/96	Abandoned	
A	STRESS RELIEF OF APCVD OXIDE FILMS/Pry	PCIUS96/06375 05/06/96	Closed	JCF
A	NITROGEN SHIELD/Van Tran	08704,227 08/27/96	5,786,278 07/29/98	
		08780,106	Abandoned in favor of FWC 08/976,928	

I-71935/0ASS (463035-826)  
1039123

10/3/2003





Reference No.		Title		Abstract		Filing Date		Priority Date		Inventor	
EA	63008	TW	JEM	DEPOSITION	02/18/97	01/05/99					Taiwan
FP	63008	PC	AJT JEM MSS	OPTIMIZING SiO <sub>2</sub> FILM CONFORMALITY IN TEOS/03 APCVD	87012445 02/18/96	107673 02/02/00					PCT
A	63265		AJT MSS	OPTIMIZATION OF SiO <sub>2</sub> FILM CONFORMALITY IN ATMOSPHERIC PRESSURE CHEMICAL VAPOR DEPOSITION	PCT/US98/02342 02/17/98	Abandoned					PCT
FP	63265	PC	AJT MSS	LOW K DIELECTRICS PREPARED FROM CROSS-LINKED PEKS (CL-PPKS) <sub>Lee</sub>	08/679,864 07/16/96	5,925,420 07/20/99					
A	63347		AJT MSS	CROSSLINKED AROMATIC POLYMERS SA LOW K DIELECTRIC <sub>Lee</sub>	PCT/US97/10575 07/14/97	Abandoned					PCT
A	63379		AJT MSS	A METHOD OF PLANARIZING A DIELECTRIC LAYER WITH REDUCED HYDROGEN DIFFUSION/ Belchin	Closed						
A	63660		AJT MSS	LOW K DIELECTRICS PREPARED FROM PECVD AND PECVD OF SELECTED SILOXANES/Lee	Hold						
A	63661		AJT MSS	HIGH TEMPERATURE ROLLER MODULE/ <sub>Leiner</sub>	09/019,349 02/05/98	5,976,258 11/02/99					
A	63662		AJT	METHOD FOR FORMING VERTICALLY EXTENDED EMBEDDED LOW K MATERIALS/ <sub>Ty</sub>	Closed						
A	63665		AJT MSS	OPTIMIZATION OF SiO <sub>2</sub> FILM CONFORMITY	Closed						
FA	63665	CN	AJT MSS	METHOD OF CONTAMINATION REDUCTION BY FORMATION OF ALL OXIDE SURFACE LAYERS/ <sub>Ballley, Brady</sub>	08/823,655 03/11/97	5,916,378 06/29/99					China
PA	63665	HK	AJT MSS	METHOD OF CONTAMINATION REDUCTION BY FORMATION OF ALL OXIDE SURFACE LAYERS/ <sub>Ballley, Brady</sub>	98804123.5 03/06/98						
FA	63665	JP	AJT MSS	METHOD OF CONTAMINATION REDUCTION BY FORMATION OF ALL OXIDE SURFACE LAYERS/ <sub>Ballley, Brady</sub>	99106669.3 09/26/00	Abandoned					Hong Kong
FA	63665	KR	AJT	METHOD OF CONTAMINATION REDUCTION BY FORMATION OF ALL OXIDE SURFACE LAYERS/ <sub>Ballley, Brady</sub>	10-539667 03/106/98						Japan
					99-7608224						South Korea

I-71935/MSS (463035-828)  
1059128

Reference No.	Inventors	Patent No./ Issue Date	Foreign Countries
EA 63665	SG MSS AJT MSS	03/05/98 9904262-4 03/06/98	Singapore
EA 63665	TW AJT MSS	87102978 03/02/98	Taiwan
EP 63665	EP AJT MSS	98910238.7 03/06/98	Europe
EP 63665	PC AJT MSS	PCT/US98/04570 03/06/98	PCT
A 63669	AJT MSS	08/746,608 11/13/96	Abandoned
EP 63669	PC AJT MSS	PCT/US97/20315 11/06/97	Abandoned
A 63672	AJT JEM	Closed	Closed
A 63673	AJT JEM MSS	5,921,560 07/13/99	
A 63674	AJT MSS	Closed	Closed
A 63675	AJT JEM	5,938,851 08/17/99	
A 63676	AJT JEM	Abandoned.	
A 63677	AJT MSS	Closed	
A 64309	AJT MSS	Combined with A-59471-3 and closed	
A 64725	AJT	Closed	

I-71935/MSS (463035-828)  
1059126

Reference No.	Class	Inventors	Serial No./ Filing Date	Patent No./ Issue Date	Foreign Country/ies
		Y. H. Hsu, Inventors			
		FLAT PLATE DISCHARGE CELL OZONE GENERATOR/S/Granado's			
A		64873			
		MSS			
		AJT			
		MSS	09/01/80	6,026,589	
			02/02/98	02/22/00	
A		64873			
		I			
		AJT	09/47/92		
		MSS	12/08/99		
			Div. of 09/01/80		
			02/02/98		
FA		64873			
		CA	2319636	Abandoned	Canada
			02/01/99		
FA		64873			
		CN	99802634.4		China
			02/01/99		
FA		64873			
		HK	01104936.8	Abandoned	Hong Kong
			07/16/01		
FA		64873			
		IL	137533	Abandoned	Israel
			02/01/99		
FA		64873			
		JP	2000-529567		Japan
			02/01/99		
FA		64873			
		KR	2000-7008430	376643	South Korea
			02/01/99	03/06/03	
FA		64873			
		SG	200004218-2	74927	Singapore
			02/01/99	08/30/02	
FA		64873			
		TW	88108719	122455	Taiwan
			01/18/99	03/16/01	
FE		64873			
		EP	99903586.6		Europe
			02/01/99		

I-71935/MSS (463035-828)  
1059128

Reference No.		Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Country/ies
FP	64873	AJT MSS	WAFER CARRIER, et al.	PCT/US99/02100 02/01/99	Closed	PCT
A	65583	AJT JEM MSS	FREE FLOATING SHIELD/DeDunney, et al.	09/098,024 01/16/98	5,849,088 12/15/98	
A	65583	AJT MSS	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEM/Bartholomew, et al.	09/185,180 11/03/98	6,056,824 05/02/00	
FP	65583	AJT MSS	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEM/Bartholomew, et al.	CP of 09/098,024 PCT/US98/25740 12/04/98	Closed	PCT
EA	65583	AJT MSS	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEM/Bartholomew, et al.	2318147 12/04/98		Canada
EA	65583	AJT MSS	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEM/Bartholomew, et al.	988136414 12/04/98		China
EA	65583	AJT MSS	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEM/Christopher A. Peabody, Jay B. DeDunney, Lawrence D. Bartholomew	01104322.0 06/21/01	Abandoned	Hong Kong
EA	65583	AJT MSS	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEM/Bartholomew, et al.	98960728.8 12/14/98	Abandoned	Europe
EA	65583	AJT MSS	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEM/Bartholomew, et al.	137315 12/04/98	Abandoned	Israel
EA	65583	AJT MSS	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEM/Bartholomew, et al.	2000-540285 12/04/98	3416114 04/04/03	Japan
EA	65583	AJT MSS	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEM/Bartholomew, et al.	2000-7007859 12/04/98	346767 07/18/02	South Korea
EA	65583	AJT MSS	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEM/Bartholomew, et al.	200003932-1 12/04/98	74790 08/30/02	Singapore
EA	65583	AJT MSS	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEM/Bartholomew, et al.	87119658 11/26/98	135711 10/27/01	Taiwan
A	65583	AJT MSS	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEM/Bartholomew, et al.	09/492,420 01/27/00	6,352,592 B1 03/05/02	
EA	65583	AJT MSS	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEM/Bartholomew, et al.	CP of 09/185,180 2304548 04/07/00	Abandoned	Canada

I-71933/MSS (46303-828)  
1029128

Reference No.		Title/Invention		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
FA	65583	2-CN	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEM/Bartholomew, et al.	09106454.1 04/10/00		China
FE	65583	2-HP	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEM/Bartholomew, et al.	06362953.5 04/07/00	Abandoned	Europe
FA	65583	2-HK	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEM/Bartholomew, et al.	0201266.3 02/21/02	Abandoned	Hong Kong
FA	65583	2-IP	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEM/Bartholomew, et al.	2000-108638 04/10/00		Japan
FA	65583	2-KR	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEM/Bartholomew, et al.	2000-00186645 04/10/00	338891 05/20/02	South Korea
FA	65583	2-MY	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEM/Bartholomew, et al.	PI20001457 04/07/00		Malaysia
FA	65583	2-SG	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEM/Bartholomew, et al.	200001878.8 03/31/00		Singapore
FA	65583	2-TW	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEM/Bartholomew, et al.	89106510 04/08/00		Taiwan
FA	65583	2-TH	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEM/Bartholomew, et al.	056644 04/03/00	Abandoned	Thailand
A	65816		CYCLOPHANE DERIVATIVES CONTAINING CROSS-LINKING GROUPS/Golden	Hold		
A	65965		LOW K DIELECTRIC INORGANIC/ORGANIC HYBRID FILMS AND METHOD OF MAKING/Rose; Lopata; Felts	09/067,704 04/28/98	6,068,884 05/30/00	
FA	65965	CA	LOW K DIELECTRIC INORGANIC/ORGANIC HYBRID FILMS AND METHOD OF MAKING/Rose; Lopata; Felts	2,330,040 04/15/99	Abandoned	Canada
FA	65965	CN	LOW K DIELECTRIC INORGANIC/ORGANIC HYBRID FILMS AND METHOD OF MAKING/Rose; Lopata; Felts	99806506.4 04/15/99		China
FA	65965	HK	LOW K DIELECTRIC INORGANIC/ORGANIC HYBRID FILMS AND METHOD OF MAKING/Rose; Lopata; Felts	01108034.0 11/15/01	Abandoned	Hong Kong
FA	65965	IL	LOW K DIELECTRIC INORGANIC/ORGANIC HYBRID FILMS AND METHOD OF MAKING/Rose; Lopata; Felts	139128 04/15/99	Abandoned	Israel

I-71935/MSS (463035-828)  
1059128

Reference No.	Title/Invention	Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
FA 65965	Lopata; Felts LOW K. DIELECTRIC INORGANIC/ORGANIC HYBRID FILMS AND METHOD OF MAKING/Rose;	2000-545704 04/15/99		Japan
FA 65965	Lopata; Felts LOW K. DIELECTRIC INORGANIC/ORGANIC HYBRID FILMS AND METHOD OF MAKING/Rose;	2000-7012019 04/15/99		South Korea
FA 65965	Lopata; Felts LOW K. DIELECTRIC INORGANIC/ORGANIC HYBRID FILMS AND METHOD OF MAKING/Rose;	200005992-8 04/15/99	76753 12/07/02	Singapore
FA 65965	Lopata; Felts LOW K. DIELECTRIC INORGANIC/ORGANIC HYBRID FILMS AND METHOD OF MAKING/Rose;	88106881 04/28/99	161126 06/19/02	Taiwan
FE 65965	Lopata; Felts LOW K. DIELECTRIC INORGANIC/ORGANIC HYBRID FILMS AND METHOD OF MAKING/Rose;	99917529.2. 04/15/99		Europe
FP 65965	Lopata; Felts LOW K. DIELECTRIC INORGANIC/ORGANIC HYBRID FILMS AND METHOD OF MAKING/Rose;	PCT/US99/08246 04/15/99	Closed	PCT
A 65965 -1	Lopata; Felts LOW K. DIELECTRIC INORGANIC/ORGANIC HYBRID FILMS AND METHOD OF MAKING/Rose;	09361,667 07/27/99		
A 65965 -2	Lopata; Felts LOW K. DIELECTRIC INORGANIC/ORGANIC HYBRID FILMS AND METHOD OF MAKING/Rose;	10/637,913 08/08/03		
A 66484	Stiffler; McGrogan CHEMICAL VAPOR DEPOSITION APPARATUS EMPLOYING LINEAR INJECTORS FOR DELIVERING GASEOUS CHEMICALS AND METHOD/Dobbin; Stiffler; McGrogan	09/113,730 07/10/98	Abandoned	
FA 66484	Stiffler; McGrogan CHEMICAL VAPOR DEPOSITION APPARATUS EMPLOYING LINEAR INJECTORS FOR DELIVERING GASEOUS CHEMICALS AND METHOD/Dobbin; Stiffler; McGrogan	88110478 06/22/99	147614 04/22/02	Taiwan
FP 66484	Stiffler; McGrogan CHEMICAL VAPOR DEPOSITION APPARATUS EMPLOYING LINEAR INJECTORS FOR	PCT/US99/08702 04/21/99	Abandoned	PCT

I-71995/MSS (463035-828)  
1039128

Reference No.	Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
P 66959	AJT MSS AJT	DELIVERING GASEOUS CHEMICALS AND METHOD/Dobias, Srdic;McGrogan	60/118,286 02/02/99	Closed	
A 66959	AJT MSS	WAFER PROCESSING REACTOR HAVING A GAS FLOW CONTROL SYSTEM AND METHOD/ Bartholomew	09/493,492 01/28/00	6,143,080 11/07/00	
EA 66959	CA AJT MSS	WAFER PROCESSING REACTOR HAVING A GAS FLOW CONTROL SYSTEM AND METHOD/ Bartholomew; Bailey; Ewald; Boland	2362694 02/01/00	Abandoned	Canada
EA 66959	CN AJT MSS	WAFER PROCESSING REACTOR HAVING A GAS FLOW CONTROL SYSTEM AND METHOD/ Bartholomew; Bailey; Ewald; Boland	09804644.1 02/01/00		China
EA 66959	HK MSS	WAFER PROCESSING REACTOR HAVING A GAS FLOW CONTROL SYSTEM AND METHOD/ Bartholomew; Bailey; Ewald; Boland	02104112.3 05/31/02	Abandoned	Hong Kong
EA 66959	IL AJT MSS	WAFER PROCESSING REACTOR HAVING A GAS FLOW CONTROL SYSTEM AND METHOD	144696 02/01/00	Abandoned	Israel
EA 66959	JP AJT MSS	WAFER PROCESSING REACTOR HAVING A GAS FLOW CONTROL SYSTEM AND METHOD	2000-599919 02/01/00		Japan
EA 66959	KR AJT MSS	WAFER PROCESSING REACTOR HAVING A GAS FLOW CONTROL SYSTEM AND METHOD	2001-7009763 02/01/00		South Korea
EA 66959	SG AJT MSS	WAFER PROCESSING REACTOR HAVING A GAS FLOW CONTROL SYSTEM AND METHOD	200104725-7 02/01/00		Singapore
EA 66959	TW AJT MSS	WAFER PROCESSING REACTOR HAVING A GAS FLOW CONTROL SYSTEM AND METHOD/ Bartholomew; Bailey; Ewald; Boland	89101846 02/02/00		Taiwan
EE 66959	EP AJT MSS	WAFER PROCESSING REACTOR HAVING A GAS FLOW CONTROL SYSTEM AND METHOD/ Bartholomew; Bailey; Ewald; Boland	009100448.8 02/21/00		Europe
EP 66959	PC AJT MSS	WAFER PROCESSING REACTOR HAVING A GAS FLOW CONTROL SYSTEM AND METHOD/ Bartholomew; Bailey; Ewald; Boland	US90/02606 02/01/00	Closed	PCI

I-71943/MSS (463031-828)  
1039128



Reference No.		Title/Inventions		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
A	66859	I	WATER PROCESSING REACTOR HAVING A GAS FLOW CONTROL SYSTEM AND METHOD/ Bacholansaw; Bailoy; Ewald; Boland;		Granted	
P	67178		GAS DELIVERY METERING TUBE/Standard; Yao; Hamilton; Ingle; DeSa; Kuchayev; Peabody	60/135,353 05/21/99		
A	67178		GAS DELIVERY METERING TUBE/Ingle; Standard; Yao; Hamilton; Young; DeSa	09/470,446 12/22/99		
FA	67178	CA	GAS DELIVERY METERING TUBE/Ingle; Standard; Yao; Hamilton; Young; DeSa	2308758 05/18/00	Abandoned	Canada
FA	67178	CN	GAS DELIVERY METERING TUBE/Ingle; Standard; Yao; Hamilton; Young; DeSa	00108583.2 05/18/00	2159108583.2 05/21/03	China
FE	67178	EP	GAS DELIVERY METERING TUBE/Ingle; Standard; Yao; Hamilton; Young; DeSa	00304190.2 03/18/00		Europe
FA	67178	HK	GAS DELIVERY METERING TUBE/Ingle; Standard; Yao; Hamilton; Young; DeSa	01102509.9 04/10/01	Abandoned	Hong Kong
FA	67178	JP	GAS DELIVERY METERING TUBE/Ingle; Standard; Yao; Hamilton; Young; DeSa	2000-148939 05/19/00		Japan
FA	67178	KR	GAS DELIVERY METERING TUBE/Ingle; Standard; Yao; Hamilton; Young; DeSa	2000-0026966 05/19/00		South Korea
FA	67178	MY	GAS DELIVERY METERING TUBE/Ingle; Standard; Yao; Hamilton; Young; DeSa	PE-200002163 05/17/00		Malaysia
FA	67178	SG	GAS DELIVERY METERING TUBE/Ingle; Standard; Yao; Hamilton; Young; DeSa	200002705-2 05/16/00		Singapore
FA	67178	TH	GAS DELIVERY METERING TUBE/Ingle; Standard; Yao; Hamilton; Young; DeSa	057695 05/18/00	Abandoned	Thailand
FA	67178	TW	GAS DELIVERY METERING TUBE/Ingle; Standard; Yao; Hamilton; Young; DeSa	89106456 04/07/00	140755 01/09/02	Taiwan
P	67178	I	IMPROVED GAS DELIVERY METERING TUBE/DeDonney; DeSa	Unfiled		
A	67178	I	GAS DELIVERY METERING TUBE/DeDonney; DeSa; Kuriba	09/905,349 07/13/01		
FA	67178	I-CN	GAS DELIVERY METERING TUBE/Ambony Desai; Jay B. DeDonney; Samuel Kuriba	02140579.0 07/12/02		China

L-71935/MSS (463035-038)  
1059128

Reference No.		Title/Invention		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
FA	67178	1-2P	GAS DELIVERY METERING TUBE/Anthony Deas; Jay B. Deatonney; Samuel Kurita	2002-206050 07/13/02		Japan
FA	67178	1-KR	GAS DELIVERY METERING TUBE/Anthony Deas; Jay B. Deatonney; Samuel Kurita	2002-0040745 07/12/02		South Korea
FA	67178	1-MY	GAS DELIVERY METERING TUBE/Anthony Deas; Jay B. Deatonney; Samuel Kurita	07/09/02		Malaysia
FA	67178	1-SG	GAS DELIVERY METERING TUBE/Anthony Deas; Jay B. Deatonney; Samuel Kurita	200204131-7 07/09/02		Singapore
FA	67178	1-TW	GAS DELIVERY METERING TUBE/Anthony Deas; Jay B. Deatonney; Samuel Kurita	91115232 07/09/02		Taiwan
FB	67178	1-EP	GAS DELIVERY METERING TUBE/Deas; DeDonnelly; Kurita	0225-49672.0 07/15/02		Europe
A	67388		METHOD FOR DEPOSITING SILICON DIOXIDE FILM AND PRODUCT/Mahawili	07/370,331 06/22/89	Abandoned	
FA	67388	JP	METHOD FOR DEPOSITING SILICON DIOXIDE FILM AND PRODUCT/Mahawili	165-499/90 06/22/90	2,918,300 04/23/99	Japan
FA	67388	ER	METHOD FOR DEPOSITING SILICON DIOXIDE FILM AND PRODUCT/Mahawili	1990-9287 06/22/90	Abandoned 162652 09/01/98	South Korea
FA	67388	TW	METHOD FOR DEPOSITING SILICON DIOXIDE FILM AND PRODUCT/Mahawili	79105124 06/22/90	Abandoned 50934-08/21/91	Taiwan
FE	67388	DE	METHOD FOR DEPOSITING SILICON DIOXIDE FILM AND PRODUCT/Mahawili	90111648.3 06/20/90	Abandoned 0404101 05/01/96	Germany
FE	67388	EP	METHOD FOR DEPOSITING SILICON DIOXIDE FILM AND PRODUCT/Mahawili	90111648.3 06/20/90	0404101 05/01/96	Europe
FE	67388	FR	METHOD FOR DEPOSITING SILICON DIOXIDE FILM AND PRODUCT/Mahawili	90111648.3 06/20/90	0404101 05/01/96	France
FE	67388	GB	METHOD FOR DEPOSITING SILICON DIOXIDE FILM AND PRODUCT/Mahawili	90111648.3 06/20/90	0404101 05/01/96	Great Britain
FE	67388	NL	METHOD FOR DEPOSITING SILICON DIOXIDE FILM AND PRODUCT/Mahawili	90111648.3 06/20/90	0404101 05/01/96	Netherlands
A	67388	I	METHOD FOR DEPOSITING SILICON DIOXIDE FILM AND PRODUCT/Mahawili	07/661,837 02/27/91	Abandoned Abandoned	

I-71913/MSS (463035-838)  
1089128

Reference No.		Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
A	67389	AJT MSS	CHEMICAL VAPOR DEPOSITION REACTOR AND METHOD OF OPERATION/Mabawili	07/386,903 07/28/89	4,993,358 02/19/91	Japan
EA	67389	AJT MSS	CHEMICAL VAPOR DEPOSITION REACTOR AND METHOD OF OPERATION/Mabawili	201089/90 07/27/90	Abandoned	Japan
EA	67389	AJT MSS	CHEMICAL VAPOR DEPOSITION REACTOR AND METHOD OF OPERATION/Mabawili	11454/1990 07/27/90	Abandoned	South Korea
EA	67389	AJT MSS	CHEMICAL VAPOR DEPOSITION REACTOR AND METHOD OF OPERATION/Mabawili	79105355 07/29/90	47787 09/26/91 Abandoned	Taiwan
EA	67389	AJT MSS	CHEMICAL VAPOR DEPOSITION REACTOR AND METHOD OF OPERATION/Mabawili	90114325.5 07/26/90	Abandoned	Europe
A	67390	AJT MSS	MULTI-ZONE PLANAR HEATER ASSEMBLY AND METHOD OF OPERATION/Mabawili	07/409,125 09/19/89	5,059,770 10/22/91	Europe
EA	67390	AJT MSS	MULTI-ZONE PLANAR HEATER ASSEMBLY AND METHOD OF OPERATION/Mabawili	242305/90 09/12/90	2133364 11/14/97	Japan
EA	67390	AJT MSS	MULTI-ZONE PLANAR HEATER ASSEMBLY AND METHOD OF OPERATION/Mabawili	14732/90 09/18/90	160310 08/19/98	South Korea
EA	67390	AJT MSS	MULTI-ZONE PLANAR HEATER ASSEMBLY AND METHOD OF OPERATION/Mabawili	79105354 07/29/90	51351 01/23/92	Taiwan
EA	67390	AJT MSS	MULTI-ZONE PLANAR HEATER ASSEMBLY AND METHOD OF OPERATION/Mabawili	90115336.1 08/10/90	0418541 06/15/94	Europe
EA	67390	AJT MSS	MULTI-ZONE PLANAR HEATER ASSEMBLY AND METHOD OF OPERATION/Mabawili	90115336.1 08/10/90	0418541 06/15/94	Germany
EA	67390	AJT MSS	MULTI-ZONE PLANAR HEATER ASSEMBLY AND METHOD OF OPERATION/Mabawili	90115336.1 08/10/90	0418541 06/15/94	France
EA	67390	AJT MSS	MULTI-ZONE PLANAR HEATER ASSEMBLY AND METHOD OF OPERATION/Mabawili	90115336.1 08/10/90	0418541 06/15/94	Netherlands
A	67391	AJT MSS	METHOD OF SOLDERING IN A CONTROLLED-CONVECTION SURFACE-MOUNT REFLOW FURNACE/Alley, Carmasi, Daley, Roffey	07/677,661 03/29/91	5,232,145 08/03/93	Great Britain
A	67392	AJT MSS	METHOD FOR PRODUCING HIGHLY CONDUCTIVE AND TRANSPARENT FILMS OF TIN AND FLUORIDE DOPED INDIUM OXIDE BY	07/668,858 03/13/91	5,172,391 06/16/92	

1-71935/MSS (463035-828)  
1059128

Reference No.		Title/Inventors		IPC Class.	IPC Class.	IPC Class.	IPC Class.	IPC Class.	IPC Class.	IPC Class.	IPC Class.	IPC Class.	IPC Class.
Class	No.	Country	Applicant	Inventor	IPC Class.	IPC Class.	IPC Class.	IPC Class.	IPC Class.	IPC Class.	IPC Class.	IPC Class.	IPC Class.
FA	67392	JP	AJT MSS	APCVD/Mayer	METHOD FOR PRODUCING HIGHLY CONDUCTIVE AND TRANSPARENT FILMS OF TIN AND FLUORIDE DOPED INDIUM OXIDE BY APCVD/Mayer	53319/92	03/12/92	Abandoned		Japan			
FA	67392	KR	AJT MSS	APCVD/Mayer	METHOD FOR PRODUCING HIGHLY CONDUCTIVE AND TRANSPARENT FILMS OF TIN AND FLUORIDE DOPED INDIUM OXIDE BY APCVD/Mayer	4652/1992	03/12/92	Abandoned		South Korea			
FE	67392	EP	AJT MSS	APCVD/Mayer	METHOD FOR PRODUCING HIGHLY CONDUCTIVE AND TRANSPARENT FILMS OF TIN AND FLUORIDE DOPED INDIUM OXIDE BY APCVD/Mayer	92003329.6	02/27/92	Abandoned		Europe			
A	67392	I	AJT MSS	APCVD/Mayer	METHOD AND APPARATUS FOR PRODUCING HIGHLY CONDUCTIVE AND TRANSPARENT FILMS OF TIN AND FLUORIDE DOPED INDIUM OXIDE BY APCVD/Mayer	07856.457	03/24/92	Abandoned					
P	67588		AJT MSS	Yuh	PROTECTIVE GAS SHIELD APPARATUS/Stockard, Yuh	60/135,362	05/21/99	Closed					
A	67588		AJT MSS	Yuh	PROTECTIVE GAS SHIELD APPARATUS/Stockard, Yuh	09/574,826	05/19/00	6,576,060					
FA	67588	CN	AJT MSS	Yuh	PROTECTIVE GAS SHIELD APPARATUS/Stockard, Yuh	09807884.X	05/19/00	06/10/03		China			
FA	67588	JP	AJT MSS	Stockard, Yuh	PROTECTIVE GAS SHIELD APPARATUS/Neil, Stockard, Yuh	2800-620151	05/19/00			Japan			
FA	67588	KR	AJT MSS	Stockard, Yuh	PROTECTIVE GAS SHIELD APPARATUS/Neil, Stockard, Yuh	2001-7014850	05/19/00			South Korea			
FA	67588	SG	AJT MSS	Stockard, Yuh	PROTECTIVE GAS SHIELD APPARATUS/Neil, Stockard, Yuh	260107153-9	03/19/00			Singapore			
FA	67588	TW	AJT MSS	Yuh	PROTECTIVE GAS SHIELD APPARATUS/Stockard, Yuh	89109705	03/19/00			Taiwan			
FE	67588	EP	AJT MSS	Yuh	PROTECTIVE GAS SHIELD APPARATUS/Stockard, Yuh	06236074.A	05/19/00			Europe			
FP	67588	PC	AJT	Stockard, Yuh	PROTECTIVE GAS SHIELD APPARATUS/Stockard, Yuh	PC/TUS000713754		closed		PCI			

I-71935/MSS (403035-828)  
1059128

Examination No.

Publication No.

Pub. No.	App. No.	Pub. No.	Pub. Date	Pub. Date	Pub. No./Issue Date	Pub. Country
P	67588	-I	MSS	05/19/00		
P	67735		AJT MSS	Unfiled		
A	67735		AJT MSS	69/127,520 04/02/99	Closed	
FA	67735	CA	AJT MSS	69/541,395 03/31/00	6,387,764 Issued: 05/14/02	
FA	67735	CN	AJT MSS	2364975 03/31/00	Abandoned	Canada
FA	67735	IL	AJT MSS	00907742.8 03/31/00		China
FA	67735	JP	AJT MSS	143608 03/31/00	Abandoned	Israel
FA	67735	KR	AJT MSS	2690-610059 03/31/00		Japan
FA	67735	SG	AJT MSS	2001-7012564 03/31/00		South Korea
FA	67735		AJT MSS	200103864-3 03/31/00		Singapore

I-71935/MSS (463035-828)  
1059128

Reference No.	Title/Inventors	Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
EA 67735	TRENCH ISOLATION PROCESS USING APCVD TEOS-OZONE TO DEPOSIT A TRENCH FILL OXIDE PRIOR TO SIDEWALL LINER OXIDATION GROWTH/ Cards; Koo; Kaplan	89106191 04/01/00		Taiwan
EB 67735	TRENCH ISOLATION PROCESS USING APCVD TEOS-OZONE TO DEPOSIT A TRENCH FILL OXIDE PRIOR TO SIDEWALL LINER OXIDATION GROWTH/ Cards; Koo; Kaplan	00919996.9 03/31/00		
EP 67735	TRENCH ISOLATION PROCESS USING APCVD TEOS-OZONE TO DEPOSIT A TRENCH FILL OXIDE PRIOR TO SIDEWALL LINER OXIDATION GROWTH/ Cards; Koo; Kaplan	PCT/US99/08650 05/31/00		PCI
P 67736	NEAR-ATMOSPHERIC CVD SYSTEM WITH VERTICALLY-STACKED PROCESS CHAMBERS/ Carvalho; Mayer; Menagh; Savage; Vaughan	60/127,532 04/02/99	Closed	
A 67736	SEMICONDUCTOR WAFER PROCESS SYSTEM WITH VERTICALLY-STACKED PROCESS CHAMBERS AND SINGLE-AXIS DUAL-WAFER TRANSFER SYSTEM/Savage; Menagh; Carvalho; Trotant; Cozzanini; Vaughan; Mayer	09/483,945 01/13/00	6,610,150 08/26/03	
EA 67736	SEMICONDUCTOR WAFER PROCESSING SYSTEM WITH VERTICALLY-STACKED PROCESS CHAMBERS AND SINGLE-AXIS DUAL-WAFER TRANSFER SYSTEM/Savage; Menagh; Carvalho; Trotant; Cozzanini; Vaughan; Mayer	2369042 03/21/00	Abandoned	Canada
EA 67736	SEMICONDUCTOR WAFER PROCESSING SYSTEM WITH VERTICALLY-STACKED PROCESS CHAMBERS AND SINGLE-AXIS DUAL-WAFER TRANSFER SYSTEM/Savage; Menagh; Carvalho; Trotant; Cozzanini; Vaughan; Mayer	008006652.3 03/21/00		China
EA 67736	SEMICONDUCTOR WAFER PROCESSING SYSTEM WITH VERTICALLY-STACKED PROCESS CHAMBERS AND SINGLE-AXIS DUAL-WAFER TRANSFER SYSTEM/Savage; Menagh; Carvalho; Trotant; Cozzanini; Vaughan; Mayer	145678 03/21/00	Abandoned	Israel

I-71935/MSS (463035-828)  
1059128

Reference No.	Title/Inventors	Filed No./ Filing Date	Publ. No./ Issue Date	Foreign Countries
KA 67736	SEMICONDUCTOR WAFER PROCESSING SYSTEM WITH VERTICALLY-STACKED PROCESS CHAMBERS AND SINGLE-AXIS DUAL-WAFER TRANSFER SYSTEM/Savage; Menagh; Carvalheira; Troiani; Cosentino; Vaughan; Mayer	2000-609844 03/21/00		Japan
KA 67736	SEMICONDUCTOR WAFER PROCESSING SYSTEM WITH VERTICALLY-STACKED PROCESS CHAMBERS AND SINGLE-AXIS DUAL-WAFER TRANSFER SYSTEM/Savage; Menagh; Carvalheira; Troiani; Cosentino; Vaughan; Mayer	2001-7012462 03/21/00		South Korea
FA 67736	SEMICONDUCTOR WAFER PROCESSING SYSTEM WITH VERTICALLY-STACKED PROCESS CHAMBERS AND SINGLE-AXIS DUAL-WAFER TRANSFER SYSTEM/Savage; Menagh; Carvalheira; Troiani; Cosentino; Vaughan; Mayer	200105951-8 03/21/00		Singapore
EA 67736	SEMICONDUCTOR WAFER PROCESSING SYSTEM WITH VERTICALLY-STACKED PROCESS CHAMBERS AND SINGLE-AXIS DUAL-WAFER TRANSFER SYSTEM/Savage; Menagh; Carvalheira; Troiani; Cosentino; Vaughan; Mayer	89106019 03/31/00		Taiwan
FE 67736	SEMICONDUCTOR WAFER PROCESSING SYSTEM WITH VERTICALLY-STACKED PROCESS CHAMBERS AND SINGLE-AXIS DUAL-WAFER TRANSFER SYSTEM/Savage; Menagh; Carvalheira; Troiani; Cosentino; Vaughan; Mayer	0091829.7 03/21/00		Europe
FP 67736	SEMICONDUCTOR WAFER PROCESSING SYSTEM WITH VERTICALLY-STACKED PROCESS CHAMBERS AND SINGLE-AXIS DUAL-WAFER TRANSFER SYSTEM/Savage; Menagh; Carvalheira; Troiani; Cosentino; Vaughan; Mayer	PCT/US00/07509 03/21/00	Closed	PCT
A 67736 1	SEMICONDUCTOR WAFER PROCESSING SYSTEM WITH VERTICALLY-STACKED PROCESS CHAMBERS AND SINGLE-AXIS DUAL-WAFER TRANSFER SYSTEM/Savage; Menagh; Carvalheira; Troiani; Cosentino; Vaughan; Mayer	09/167,659 01/22/01 Divisional of 09/483,943 filed 01/13/00		
A 67736 2	SEMICONDUCTOR WAFER PROCESSING SYSTEM WITH VERTICALLY-STACKED PROCESS	09/996,869		

F-7195/MSS (46305-828)  
1059128

Reference No.

			File/Inventors	Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
P	67737	MSS	CHAMBERS AND SINGLE-AXIS DUAL-WAFER TRANSFER SYSTEM/Savage; Menagh; Carvalhina; Troiani; Cosentino; Yangling; Mayer	11/27/01		
P	68017	AJT MSS WEN	SINGLE-AXIS DUAL-WAFER TRANSFER SYSTEM/Troiani; Cosentino	60/127,650 04/02/99	Merged into P-67736 & Closed	
A	68017	AJT MSS WEN	IMPROVED SURFACE COMPOSITION AND METHOD FOR METAL COMPONENTS/Bailey; Michael; Kans	60/130,783 04/23/99	Closed	
FA	68017	CA	CHEMICAL VAPOR DEPOSITION SYSTEM/Bailey; Michael; Kans	09/480,730 01/06/00	6,286,973 03/27/01	Canada
EA	68017	CN	CHEMICAL VAPOR DEPOSITION SYSTEM/Bailey; Michael; Kans	2371353 03/03/00	Abandoned	
EA	67017	IL	CHEMICAL VAPOR DEPOSITION SYSTEM/Bailey; Michael; Kans	00808554.4 03/03/00		China
EA	68017	JP	CHEMICAL VAPOR DEPOSITION SYSTEM/Bailey; Michael; Kans	146135 03/03/00	Abandoned	Israel
EA	68017	ER	CHEMICAL VAPOR DEPOSITION SYSTEM/Bailey; Michael; Kans	2000-613851 03/03/00		Japan
EA	68017	SG	CHEMICAL VAPOR DEPOSITION SYSTEM/Bailey; Michael; Kans	2001-7013598 03/03/00		South Korea
EA	68017	TW	CHEMICAL VAPOR DEPOSITION SYSTEM/Bailey; Michael; Kans	20010613-5 03/03/00		Singapore
EB	68017	EP	CHEMICAL VAPOR DEPOSITION SYSTEM/Bailey; Michael; Kans	89104318 03/13/00		Taiwan
EP	68017	PC	CHEMICAL VAPOR DEPOSITION SYSTEM/Bailey; Michael; Kans	00912173.2 03/03/00		Europe
A	68017	I	CHEMICAL VAPOR DEPOSITION SYSTEM AND METHOD/Bailey; Michael; Kans	PCT/US00/05630 03/03/00	Closed	PCT
				09/704,644 11/01/00	6,485,783	

F-71935/MSS (463035-428)  
1059128



Reference No.	Classification	Title/Inventors	Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
F 68048	WEN AJT MSS WEN	EQUAL FLOW BELT GAS DELIVERY APTARAYU/Bartholomew; Yuh; Sumbao; King; Chan	60/134,443 05/17/99	11/26/02 Closed	
A 68048	AJT MSS WEN	GAS DISTRIBUTION SYSTEM/Bartholomew; Yuh; Sumbao; King; Chan	09/494,620 01/31/00	Abandoned	
FA 68048	CA AJT MSS WEN	GAS DISTRIBUTION SYSTEM/Bartholomew; Yuh; Sumbao; King; Chan	230832 05/15/00	Abandoned	Canada
FA 68048	CN AJT MSS WEN	GAS DISTRIBUTION SYSTEM/Bartholomew; Yuh; Sumbao; King; Chan	06108549.2 05/17/00		China
FE 68048	RP AJT MSS WEN	GAS DISTRIBUTION SYSTEM/Bartholomew; Yuh; Sumbao; King; Chan	00304070.6 05/15/00		Europe
FA 68048	HK AJT MSS WEN	GAS DISTRIBUTION SYSTEM/Bartholomew; Yuh; Sumbao; King; Chan	01102640.9 04/12/01	Abandoned	Hong Kong
FA 68048	JP AJT MSS WEN	GAS DISTRIBUTION SYSTEM/Bartholomew; Yuh; Sumbao; King; Chan	2000-144513 05/17/00		Japan
FA 68048	KR AJT MSS WEN	GAS DISTRIBUTION SYSTEM/Bartholomew; Yuh; Sumbao; King; Chan	2000-0026027 05/16/00		South Korea
FA 68048	MY AJT MSS WEN	GAS DISTRIBUTION SYSTEM/Bartholomew; Yuh; Sumbao; King; Chan	P20002031 05/10/00		Malaysia
FA 68048	SG AJT MSS WEN	GAS DISTRIBUTION SYSTEM/Bartholomew; Yuh; Sumbao; King; Chan	200002470-3 05/09/00	87112 10/16/02	Singapore
FA 68048	TH AJT MSS WEN	GAS DISTRIBUTION SYSTEM/Bartholomew; Yuh; Sumbao; King; Chan	057654 05/16/00	Abandoned	Thailand
FA 68048	TW AJT	GAS DISTRIBUTION SYSTEM/Bartholomew; Yuh;	89109368		Taiwan

I-71935/MSS (463035-828)  
1059128

Reference No.	Title/Inventors	Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
A	Stambez, King, Chan GAS DISTRIBUTION SYSTEM/Heartholmow; Yuh, Mueg; King, Chan	05/16/00	Abandoned	
F	68048 1 68073 CHEMICAL VAPOR DEPOSITION OF SILICON DIOXIDE BY USING ALKYL-SILOXANE OLIGOMERS WITH OZONE FOR SUB 0.18 MICRON DEVICE APPLICATIONS IN VLSI/; Yuh	10/21/99 08/14/02	Closed	
A	68073 CHEMICAL VAPOR DEPOSITION OF SILICON DIOXIDE BY USING ALKYL-SILOXANE OLIGOMERS WITH OZONE FOR SUB 0.18 MICRON DEVICE APPLICATIONS IN VLSI/; Yuh	09/30/02 04/04/00	6465044 10/15/02	
EA	68073 CN CHEMICAL VAPOR DEPOSITION OF SILICON OXIDE FILMS USING ALKYL-SILOXANE OLIGOMERS WITH OZONE/; Yuan	09811030.1 06/15/00		China
EA	68073 JP CHEMICAL VAPOR DEPOSITION OF SILICON OXIDE FILMS USING ALKYL-SILOXANE OLIGOMERS WITH OZONE/; Yuan	2001-509075 06/15/00		Japan
EA	68073 KR CHEMICAL VAPOR DEPOSITION OF SILICON OXIDE FILMS USING ALKYL-SILOXANE OLIGOMERS WITH OZONE/; Yuan	2002-7000308 06/15/00		South Korea
EA	68073 SG CHEMICAL VAPOR DEPOSITION OF SILICON OXIDE FILMS USING ALKYL-SILOXANE OLIGOMERS WITH OZONE/; Yuan	06/15/00		Singapore
EA	68073 TW CHEMICAL VAPOR DEPOSITION OF SILICON OXIDE FILMS USING ALKYL-SILOXANE OLIGOMERS WITH OZONE	89113435 07/06/00	153183 07/25/02	Taiwan
FE	68073 EP CHEMICAL VAPOR DEPOSITION OF SILICON OXIDE FILMS USING ALKYL-SILOXANE OLIGOMERS WITH OZONE/; Yuan	00939940.3 06/15/00		Europe
EP	68073 PC CHEMICAL VAPOR DEPOSITION OF SILICON OXIDE FILMS USING ALKYL-SILOXANE OLIGOMERS WITH OZONE	PCT/US00/16642 06/15/00	Closed	PCT
P	68244 METHOD FOR IN-SITU CLEANING OF SILICON	60/143,285	Closed	

I-71932/MSS (43 035-828)  
1089128

Reference No.	Pub. No./Inventors	Serial No./ Pub. Date	Patent No./ Issue Date	Country
A	68244 AJT MSS	07/12/99	6,544,345 04/08/03	Korea China
FA	68244 AJT MSS	09/15/03 07/12/00		China
FA	68244 AJT MSS	80811232.0 07/12/00		Japan
FA	68244 AJT MSS	2001-509320 07/12/00		South Korea
FA	68244 AJT MSS	2002-7000480 07/12/00		Singapore
FA	68244 AJT MSS	200200181-6 07/12/00		Taiwan
FB	68244 AJT MSS	89113887 07/18/00		Europe
FP	68244 AJT MSS	00938006.9 07/12/00		PCT
P	68628 AJT	PC7U900/40359 07/12/00	Closed	
		60166,662	Closed	

F-71935/MSS (463031-828)  
1059128

Reference No.	Inventors	Title/Inventors	Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
A	68628	INORGANIC/ORGANIC DIELECTRIC FILMS/Lopata; Felts	11/19/92		
FA	68628	SYSTEM AND METHOD FOR DEPOSITING INORGANIC/ORGANIC DIELECTRIC FILMS/Lopata; Felts	09/15/83 11/17/00		
FA	68628	SYSTEM AND METHOD FOR DEPOSITING INORGANIC/ORGANIC DIELECTRIC FILMS/Lopata; Felts	0081628-A 11/17/00		China
FA	68628	SYSTEM AND METHOD FOR DEPOSITING INORGANIC/ORGANIC DIELECTRIC FILMS/Lopata; Felts	2001-538378 11/17/00		Japan
FA	68628	SYSTEM AND METHOD FOR DEPOSITING INORGANIC/ORGANIC DIELECTRIC FILMS/Lopata; Felts	11/17/00		South Korea
FA	68628	SYSTEM AND METHOD FOR DEPOSITING INORGANIC/ORGANIC DIELECTRIC FILMS/Lopata; Felts	P20003431 11/20/00		Malaysia
FA	68628	SYSTEM AND METHOD FOR DEPOSITING INORGANIC/ORGANIC DIELECTRIC FILMS/Lopata; Felts	11/17/00		Singapore
FA	68628	SYSTEM AND METHOD FOR DEPOSITING INORGANIC/ORGANIC DIELECTRIC FILMS/Lopata; Felts	89124488 11/18/00		Taiwan
FE	68628	SYSTEM AND METHOD FOR DEPOSITING INORGANIC/ORGANIC DIELECTRIC FILMS/Lopata; Felts	00980511.0 11/17/00		Europe
FP	68628	SYSTEM AND METHOD FOR DEPOSITING INORGANIC/ORGANIC DIELECTRIC FILMS/Lopata; Felts	PCT/US00/31694 11/17/00	Closed	PCI
A	68894	CHEMICAL VAPOR DEPOSITION APPARATUS/Campbell; Miller	06/412,237 08/12/82	4,545,327 10/08/85	
FA	68894	CHEMICAL VAPOR DEPOSITION APPARATUS AND PROCESS/Campbell; Miller	1848083 08/26/83	538152 08/26/83 Abandoned	Australia
FA	68894	CHEMICAL VAPOR DEPOSITION APPARATUS AND PROCESS/Campbell; Miller	435,134 08/23/83	1,196,777 11/19/85	Canada

L-71935/MSS (463014-828)  
1059128

Reference No.	Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Country/ies
FA 68894	IL	AJT MSS	69170	Abandoned	
FA 68894	IL-1	AJT MSS	07/05/83	Abandoned	Israel
FA 68894	IP	AJT MSS	80079	80879 07/01/87	Israel
FA 68894	IP	AJT MSS	15517/83	Abandoned	
FA 68894	IP	AJT MSS	08/26/83	1446905 06/30/88	Japan
A 68894	I	AJT MSS	83304889.5	Abandoned	Europe
A 68895		AJT MSS	06/657,313 10/02/84	4,547,404 10/15/85	
FA 68895	AU	AJT MSS	06/528,193 08/31/83	4,539,933 09/10/85	
FA 68895	CA	AJT MSS	32,564/84 08/30/84	57,283 08/30/84 Abandoned	Australia
FA 68895	CA-1	AJT MSS	462,110 08/30/84	1,216,419 01/13/87	Canada
FA 68895	TW	AJT MSS	515,262 08/01/86	Abandoned 1,236,970 05/24/88	Canada
FA 68895	IP	AJT MSS	73103596 08/30/84	Abandoned 23307 12/28/85	Taiwan
A 68896		AJT MSS	84303932.0 08/30/84	Abandoned 0137702 03/21/90	Europe
FA 68896	IP	AJT MSS	06/628,542 07/06/84	Abandoned 4,548,159 10/22/85	
FA 68896	IP	AJT MSS	14685785 07/05/85	1451172 07/25/88 Abandoned	Japan

F-7193/MSS (463035-028)  
1059128

Reference No.	Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
A	68897	AJT, MSS	CHEMICAL VAPOR DEPOSITION WAFER BOAT/ Loram; DuBois	66/607,065 05/04/84	
EA	68897	CA	CHEMICAL VAPOR DEPOSITION WAFER BOAT/ Loram; DuBois	460,118 04/23/85	Canada
EA	68897	JP	CHEMICAL VAPOR DEPOSITION WAFER BOAT/ Loram; DuBois	9395785 05/02/85	Japan
A	68897	I	CHEMICAL VAPOR DEPOSITION WAFER BOAT/ Loram; DuBois	66/804,934 12/03/85	
A	68897	2	CHEMICAL VAPOR DEPOSITION WAFER BOAT/ Loram; DuBois	Continuation of 06/607,065 06/828,625 02/10/86	
A	68898	AJT, MSS	PRIMARY FLOW CVD APPARATUS COMPRISING GAS PREHEATER AND MEANS FOR SUBSTANTIALLY BODY-FREE GAS FLOW/Loram; DuBois; Miller; Sellheimer	4,694,778 09/22/87	
EA	68898	CA	PRIMARY FLOW CVD APPARATUS AND METHOD/ Loram; DuBois; Miller; Sellheimer	Abandoned 06/14/94	
EA	68898	JP	PRIMARY FLOW CVD APPARATUS AND METHOD/ Loram; DuBois; Miller; Sellheimer	2,109,198 04/09/92	Canada
EA	68898	KR	PRIMARY FLOW CVD APPARATUS AND METHOD/ Loram; DuBois; Miller; Sellheimer	51086292 04/09/92	Japan
FE	68898	CH	PRIMARY FLOW CVD APPARATUS AND METHOD/ Loram; DuBois; Miller; Sellheimer	703234/1993 10/25/93	South Korea
FE	68898	DE	PRIMARY FLOW CVD APPARATUS AND METHOD/ Loram; DuBois; Miller; Sellheimer	92911855.2 04/09/92	Switzerland
FE	68898	EP	PRIMARY FLOW CVD APPARATUS AND METHOD/ Loram; DuBois; Miller; Sellheimer	Abandoned 69230401.0 12/08/99	Germany
FE	68898	FR	PRIMARY FLOW CVD APPARATUS AND METHOD/ Loram; DuBois; Miller; Sellheimer	6585343 12/08/99	France
			PRIMARY FLOW CVD APPARATUS AND METHOD/ Loram; DuBois; Miller; Sellheimer	6585343 05/25/01	
			PRIMARY FLOW CVD APPARATUS AND METHOD/ Loram; DuBois; Miller; Sellheimer	0267520 07/05/00	
			PRIMARY FLOW CVD APPARATUS AND METHOD/ Loram; DuBois; Miller; Sellheimer	0585343 12/08/99	
			PRIMARY FLOW CVD APPARATUS AND METHOD/ Loram; DuBois; Miller; Sellheimer	92911855.2 04/09/92	
			PRIMARY FLOW CVD APPARATUS AND METHOD/ Loram; DuBois; Miller; Sellheimer	92911855.2 04/09/92	
			PRIMARY FLOW CVD APPARATUS AND METHOD/ Loram; DuBois; Miller; Sellheimer	92911855.2 04/09/92	

I-71935/MSS (463035-828)  
1059128

Reference No.		Inventors		Serial No./ Filing Date		Patent No./ Issue Date		Foreign Countries	
FE	68898	GB	MSS	Learn; Dubois; Miller; Sellheimer	04/02/92	12/08/99		France	
FE	68898	IT	AJT	PRIMARY FLOW CVD APPARATUS AND METHOD/ Learn; Dubois; Miller; Sellheimer	92911855.2	0585343		United Kingdom	
FE	68898	NL	MSS	PRIMARY FLOW CVD APPARATUS AND METHOD/ Learn; Dubois; Miller; Sellheimer	04/09/92	12/06/99		Italy	
FE	68898	NL	AJT	PRIMARY FLOW CVD APPARATUS AND METHOD/ Learn; Dubois; Miller; Sellheimer	92911855.2	0585343		Italy	
FE	68898	PC	MSS	PRIMARY FLOW CVD APPARATUS AND METHOD/ Learn; Dubois; Miller; Sellheimer	92911855.2	0585343		Netherlands	
A	68899		AJT	PRIMARY FLOW CVD APPARATUS AND METHOD/ Learn; Dubois; Miller; Sellheimer	04/09/92	12/08/99		Netherlands	
A	68899	1	MSS	THERMAL PROCESSING APPARATUS AND PROCESS/Porter; Sanchez; Kowalski	PCT/US92/02666	Closed		PCI	
EP	68899	1-PC	AJT	THERMAL PROCESSING APPARATUS AND PROCESS/Porter; Sanchez; Kowalski	08/398,108	5,626,680			
EP	68899	1-EP	MSS	THERMAL PROCESSING APPARATUS AND PROCESS/Porter; Sanchez; Kowalski	03/03/95	05/06/97			
EP	68899	1-EP	AJT	THERMAL PROCESSING APPARATUS AND PROCESS/Porter; Sanchez; Kowalski	08/565,177	5,679,168			
EP	68899	1-EP	MSS	THERMAL PROCESSING APPARATUS AND PROCESS/Porter; Sanchez; Kowalski	11/28/95	10/21/97			
EP	68899	1-PC	AJT	THERMAL PROCESSING APPARATUS AND PROCESS/Porter; Sanchez; Kowalski	CIP of 08/399,108	Closed		PCI	
EP	68899	1-EP	MSS	THERMAL PROCESSING APPARATUS AND PROCESS/Porter; Sanchez; Kowalski	PCT/US96/02440	Closed		PCI	
EP	68899	1-EP	AJT	THERMAL PROCESSING APPARATUS AND PROCESS/Porter; Sanchez; Kowalski	03/04/96			Europe	
EP	68899	1-EP	MSS	THERMAL PROCESSING APPARATUS AND PROCESS/Porter; Sanchez; Kowalski	96906598.6			Europe	
EP	68899	1-KR	AJT	THERMAL PROCESSING APPARATUS AND PROCESS/Porter; Sanchez; Kowalski	03/04/96			Japan	
EP	68899	1-KR	MSS	THERMAL PROCESSING APPARATUS AND PROCESS/Porter; Sanchez; Kowalski	526895/96			Japan	
EP	68899	2	AJT	THERMAL PROCESSING APPARATUS AND PROCESS/Porter; Sanchez; Kowalski	09/01/97			South Korea	
EP	68899	2-PC	MSS	THERMAL PROCESSING APPARATUS AND PROCESS/Kobla, Jr.; Dip; Engdahl; Oliver; Radtiff	706100/1997			South Korea	
EP	68899	2-EP	AJT	THERMAL PROCESSING APPARATUS AND PROCESS/Kobla, Jr.; Dip; Engdahl; Oliver; Radtiff	09/02/97			South Korea	
EP	68899	2-EP	MSS	THERMAL PROCESSING APPARATUS AND PROCESS/Kobla, Jr.; Dip; Engdahl; Oliver; Radtiff	08/563,875	5,618,551			
EP	68899	2-EP	AJT	THERMAL PROCESSING APPARATUS AND PROCESS/Kobla, Jr.; Dip; Engdahl; Oliver; Radtiff	11/28/95	04/08/97			
EP	68899	2-EP	MSS	THERMAL PROCESSING APPARATUS AND PROCESS/Kobla, Jr.; Dip; Engdahl; Oliver; Radtiff	CIP of 08/399,108	Closed		PCI	
EP	68899	2-EP	AJT	THERMAL PROCESSING APPARATUS AND PROCESS/Kobla, Jr.; Dip; Engdahl; Oliver; Radtiff	PCT/US96/18731	Closed		PCI	
EP	68899	2-EP	MSS	THERMAL PROCESSING APPARATUS AND PROCESS/Kobla, Jr.; Dip; Engdahl; Oliver; Radtiff	11/22/96			Europe	
EP	68899	2-EP	AJT	THERMAL PROCESSING APPARATUS AND PROCESS/Kobla, Jr.; Dip; Engdahl; Oliver; Radtiff	96941440.R	0864170		Europe	
EP	68899	2-EP	MSS	THERMAL PROCESSING APPARATUS AND PROCESS/Kobla, Jr.; Dip; Engdahl; Oliver; Radtiff	11/22/96			Japan	
EP	68899	2-EP	AJT	THERMAL PROCESSING APPARATUS AND PROCESS/Kobla, Jr.; Dip; Engdahl; Oliver; Radtiff	520565/97			Japan	
EP	68899	2-EP	MSS	THERMAL PROCESSING APPARATUS AND PROCESS/Kobla, Jr.; Dip; Engdahl; Oliver; Radtiff	11/22/96			South Korea	
EP	68899	2-EP	AJT	THERMAL PROCESSING APPARATUS AND PROCESS/Kobla, Jr.; Dip; Engdahl; Oliver; Radtiff	702960/1998			South Korea	
EP	68899	2-EP	MSS	THERMAL PROCESSING APPARATUS AND PROCESS/Kobla, Jr.; Dip; Engdahl; Oliver; Radtiff	11/22/96			South Korea	

I-7193/MSS (463035-026)  
1039128

Reference No.		Title/Inventors		Serial No./ Filing Date	Issue No./ Issue Date	Foreign Countries
FA	68992	2-TW	AJT MSS	86101168 01/31/87	NI-094773 08/11/98	Taiwan
A	68990		AJT MSS	06/719,409 04/03/85	4,636,140 01/13/87	
A	68990	1	AJT MSS	06/880,460 06/30/86 Div. of 06/719,409	4,721,424 01/26/88 Abandoned	
A	68990	2	AJT MSS	06/880,422 06/30/86 Div. of 06/719,409	Reinstated 4,692,115 09/08/87	
A	68990	3	AJT MSS	06/880,423 06/30/86 Div. of 06/719,409	Abandoned 4,684,863 08/04/87	
A	68991		AJT MSS	06/919,736 10/16/86	Abandoned 4,711,197 12/08/87	
FA	68991	CA	AJT MSS	545,025 08/21/87	Abandoned 1,277,442 12/04/90	Canada
FA	68991	JP	AJT MSS	26150787 10/16/87	Abandoned 2642936 05/02/97	Japan
A	68992		AJT MSS	08/827,542 03/28/97	6,005,225 12/21/99	
FA	68992	KR	AJT MSS	107871998 03/27/98		South Korea
FA	68992	JP	AJT MSS	95186698 03/25/98		Japan
FA	68992	TW	AJT MSS	87104418 63/24/98		Taiwan
FE	68992	EP	AJT MSS	98301618.9 03/05/98		Europe
A	68992	1	AJT	09/822,057	6,039,567	

I-71935/MSS (463035-828)  
1059128



Reference No.	Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
EA 68902	MSS	RECIRCULATING HEATER EXHAUST COOLING SYSTEM/Boltov; Wisen	02/10/98 CIP of 08/827,542	05/09/00	
EA 68902	AJT MSS	SEMICONDUCTOR THERMAL PROCESSOR	1531189 02/08/99		Australia
FE 68902	AJT MSS	RECIRCULATING HEATER/Boltov; Wisen	2,261,391 02/08/99		Canada
FE 68902	AJT MSS	SEMICONDUCTOR THERMAL PROCESSOR	99300910.9 02/09/99		Europe
FE 68902	AJT MSS	RECIRCULATING HEATER/Boltov; Wisen	00100999.1 02/18/00		Hong Kong
FA 68902	AJT MSS	SEMICONDUCTOR THERMAL PROCESSOR	11-072438 02/10/99		Japan
FA 68902	AJT MSS	RECIRCULATING HEATER/Boltov; Wisen	4492/1999 02/09/99		South Korea
A 68903	AJT MSS/WEN	DOUBLE WALL REACTION CHAMBER	09/022,056 02/10/98	6,101,844 08/15/00	
FA 68903	AJT MSS	GLASSWARE/Fowler; Parvin; Kowalski; Wisen	15512/99 02/08/99	746022 07/25/02	Australia
FA 68903	AJT MSS	DOUBLE WALL REACTION CHAMBER	2,261,394 02/08/99	Abandoned	Canada
FA 68903	AJT MSS	DOUBLE WALL REACTION CHAMBER	11-072437 02/10/99		Japan
FA 68903	AJT MSS	DOUBLE WALL REACTION CHAMBER	4491/1999 02/09/99		South Korea
FE 68903	AJT MSS	DOUBLE WALL REACTION CHAMBER	99300909.1 02/09/99		Europe
FE 68903	AJT MSS	DOUBLE WALL REACTION CHAMBER	00100998.2 02/18/00	Abandoned	Hong Kong
P 68905	AJT MSS	LINEAR RPT REACTOR/Kowalski; Rahlff; Suh; Qiu	60/096,283 08/12/98	Closed	
A 68905	AJT MSS	HOT WALL RAPID THERMAL PROCESSOR/Rahlff; Qiu; Kowalski; Yascolich; Sobel	09/373,894 08/12/99	6,300,600 10/09/01	
P 68905	AJT	HOT WALL RAPID THERMAL PROCESSOR/Rahlff	60217,321	Closed	

I-71935/MSS (463035-028)  
1029128

Reference No.	Exhib/Invention	Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
A	68905 1 MSS AJT	0707/00		
EP	68905 1-PC MSS AJT	09/638,143 08/11/00	6,462,310 10/08/02	
EA	68905 1-CN MSS AJT	PCVUS80/2202 08/11/00	Closed	PCI
EA	68905 1-JP MSS AJT	60812823.5 08/11/00		China
EA	68905 1-KR MSS AJT	2001-517110 08/11/00		Japan
EA	68905 1-MY MSS AJT	2002-7001786 08/11/00		South Korea
EA	68905 1-SG MSS AJT	P1 20003683 08/11/00		Malaysia
EA	68905 1-TW MSS AJT	Unfiled		Singapore
EP	68905 1-EP MSS AJT	89116281 08/11/00	149415 05/17/02	Taiwan
A	68905 2 MSS AJT	06957426.0 08/11/00	6,492,621 12/10/02	Europe
A	68905 3 MSS AJT	09534952 08/21/01		
A	68905 4 MSS AJT	10262215 09/30/02		
A	68905 5 MSS AJT	10261963 09/30/02		
A	68906 MSS AJT	Unfiled		
A	68907 MSS AJT	06529415 09/06/83	4,524,719 06/23/85	
A	68907 MSS AJT	066899923	4,720,395	

I-71935/MSS (463035-828)  
1059128

Reference No.	Title/Invention	Serial No./ Filing Date	Patent No./ Issues Date	Foreign Countries
A	PROCESS	08/25/86	01/19/88	
A	PULSE WIDTH MODULATED PRESSURE CONTROL SYSTEM FOR CHEMICAL VAPOR DEPOSITION APPARATUS/Johnson; Elliott	06/245,212 03/27/86 CIP of 06/813,915	Abandoned 4,728,869 03/01/88	
A	HOT WALL DIFFUSION FURNACE AND METHOD FOR OPERATING THE FURNACE/Doyle; Ernest	07/181,787 04/13/88	4,886,954 12/12/89	
A	METHOD AND APPARATUS FOR REMOVAL OF BY-PRODUCTS OF CHEMICAL VAPOR DEPOSITION FROM OIL FOR VACUUM PUMP/Foster	06/039,523 04/12/79	4,228,004 10/14/80	
A	MASS FLOW CONTROLLER/Doyle	06/193,876 10/03/80	4,638,855 04/21/87	
A	DIFFUSION FURNACE MULTIZONE TEMPERATURE CONTROL/Doyle	06/864,676 05/19/86	4,711,989 12/08/87	
A	WAFER BOAT TRANSFER TOOL/Mello	06/863,963 05/16/86	4,728,246 03/01/88	
A	WAFER TRANSFER STAND/Sanders; Taylor	07/048,668 05/12/87	Abandoned 4,721,427 01/26/88	
A	TEMPERATURE SENSOR FOR BATCH-TYPE REACTOR/Ohrt	09/024,500 02/17/78	Abandoned Reinstated Abandoned	
A	LAYERED BLOCK FLUID DELIVERY SYSTEM/Nguyen	09/388,216 09/01/79	Abandoned	
FA	LAYERED BLOCK FLUID DELIVERY SYSTEM/Nguyen	89116370 08/14/00	140378 08/21/01	Taiwan
FP	LAYERED BLOCK FLUID DELIVERY SYSTEM/Nguyen	US0021227 08/03/00	Abandoned	PCT

I-71938/MSS (46035-828)  
1029128

Reference No.	Title/Inventors	Essential No./ Filing Date	Priority No./ Issue Date	Foreign Countries
A	68916	AJT MSS VRI	MODULAR FLUID DELIVERY SYSTEM/NGUYEN 03/06/01	
EA	68916	1-CN	03/06/01	China
EA	68916	1-JP	CIP of 09/388,216 09/01/99	Japan
EA	68916	1-KR	02186830.5 03/05/02	South Korea
EA	68916	1-MY	2002-059114 03/05/02	Malaysia
EA	68916	1-SG	PI20020747 03/01/02	Singapore
EA	68916	1-TW	200201201-1 02/27/02	Taiwan
FE	68916	1-EP	91103478 02/26/02	Europe
F	69013	AJT MSS	02251573.8 03/06/02	Co-owned with Dupont
A	69013	AJT MSS	03/04/01 (filed by De Pont)	
A	69173	MSS	Unfiled	
A	69174	MSS	Unfiled	
P	69174	1	09/028,471 07/31/00	Co-owned with MIT, all foreign as well
A	69174	1	60/258,931 12/29/00	
A	69174	1	10/029,080 12/21/01	Co-owned with MIT, all foreign as well

F-71935/MSS (663035-028)  
1059128

Reference No.	Applicant	Title/Inventors	Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
FA 69174	I-CN	MSS	IN-SITU METHOD AND APPARATUS FOR END POINT DETECTION	N/A	China
FA 69174	I-JP	MSS	IN-SITU METHOD AND APPARATUS FOR END POINT DETECTION	07/31/01	Japan
FA 69174	I-KR	MSS	IN-SITU METHOD AND APPARATUS FOR END POINT DETECTION	2002-516605 01/31/01	S. Korea
FA 69174	I-MY	AUT	IN-SITU METHOD AND APPARATUS FOR END POINT DETECTION IN CHEMICAL MECHANICAL POLISHING/Name; Subst; Oh	PI 20013602 07/31/01	Malaysia
FA 69174	I-SG	MSS	IN-SITU METHOD AND APPARATUS FOR END POINT DETECTION	2003-004662-4 01/31/01	Singapore
FA 69174	I-TW	MSS	IN-SITU METHOD AND APPARATUS FOR END POINT DETECTION IN CHEMICAL MECHANICAL POLISHING/Name; Subst; Oh	90118624 07/31/01	Taiwan
FA 69174	I-PC	MSS	IN-SITU METHOD AND APPARATUS FOR END POINT DETECTION IN CHEMICAL MECHANICAL POLISHING/Name; Subst; Oh	FCYUS01/24146 07/31/01	PGT
A 69175		MSS	APPARATUS AND METHOD FOR CHEMICAL MECHANICAL POLISHING OF SUBSTRATES/Melvin; Sub; Oh	09/628,563 07/31/00	Co-owned with MIT, all foreign as well
FA 69175	MY	MSS	APPARATUS AND METHOD FOR CHEMICAL MECHANICAL POLISHING OF SUBSTRATES/Melvin; Sub; Oh	PI20013601 07/30/01	Malaysia
FA 69175	TW	MSS	APPARATUS AND METHOD FOR CHEMICAL MECHANICAL POLISHING OF SUBSTRATES/Melvin; Sub; Oh	90118623 07/31/01	Taiwan
P 69175	I	MSS	APPARATUS AND METHOD FOR CHEMICAL MECHANICAL POLISHING OF SUBSTRATES/Melvin; Sub; Oh	60259,016 12/29/00	Closed
FA 69175	I-CN	MSS	APPARATUS AND METHOD FOR CHEMICAL MECHANICAL POLISHING OF SUBSTRATES/Melvin; Sub; Oh	30030139 12/29/00	Co-owned with MIT, all foreign as well
FA 69175	I-CN	MSS	APPARATUS AND METHOD FOR CHEMICAL MECHANICAL POLISHING	01815145.0 01/31/01	China

I-71935/MSS (463035-828)  
1059128

Reference No.	Title/Inventors	Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries	
FA 69175	1-JP	MSS	APPARATUS AND METHOD FOR CHEMICAL MECHANICAL POLISHING	2002-512445 01/31/01	Japan
FA 69175	1-KR	MSS	APPARATUS AND METHOD FOR CHEMICAL MECHANICAL POLISHING	2003-7001395 01/31/01	South Korea
FA 69175	1-SG	MSS	APPARATUS AND METHOD FOR CHEMICAL MECHANICAL POLISHING	2003008578-0 01/31/01	Singapore
FA 69175	1-EP	MSS	APPARATUS AND METHOD FOR CHEMICAL MECHANICAL POLISHING	1962336.2 01/31/01	Europe
EP 69175	1-PC	MSS	APPARATUS AND METHOD FOR CHEMICAL MECHANICAL POLISHING OF SUBSTRATES/Melvin; Sub; Oh	PCTUS01/41513 07/31/01	PCT
A 69175	2	MSS	APPARATUS AND METHOD FOR CHEMICAL MECHANICAL POLISHING OF SUBSTRATES/Sub; Melvin; Oh	Closed	
A 69228		MSS	METHOD OF CHEMICAL MECHANICAL POLISHING/ Lat; Saks; Oh	6,458,013 10/01/02	Co-owned with MIT, all foreign as well
FA 69228	CN	MSS	METHOD OF CHEMICAL MECHANICAL POLISHING/ Lat; Saks; Oh	01815147.7 07/31/01	China
FA 69228	JP	MSS	METHOD OF CHEMICAL MECHANICAL POLISHING/ Lat; Saks; Oh	2002-515446 07/31/01	Japan
FA 69228	KR	MSS	METHOD OF CHEMICAL MECHANICAL POLISHING/ Lat; Saks; Oh	2003-7001400 07/31/01	South Korea
FA 69228	MY	MSS	METHOD OF CHEMICAL MECHANICAL POLISHING/ Lat; Saks; Oh	P20013603 07/31/01	Malaysia
EP 69228	PC	MSS	METHOD OF CHEMICAL MECHANICAL POLISHING/ Lat; Saks; Oh	PCTUS01/24170 07/31/01	PCT
FA 69228	SG	MSS	METHOD OF CHEMICAL MECHANICAL POLISHING/ Lat; Saks; Oh	240300663-2 07/31/01	Singapore
FA 69228	TW	MSS	METHOD OF CHEMICAL MECHANICAL POLISHING/ Lat; Saks; Oh	90118625 07/31/01	Taiwan
FE 69228	EP	MSS	METHOD OF CHEMICAL MECHANICAL POLISHING/ Lat; Saks; Oh	01957381.5 07/31/01	Europe
P 69229		MSS	MECHANISMS OF MATERIAL REMOVAL IN THE CHEMICAL MECHANICAL POLISHING PROCESS/	60263,813 01/23/01	Closed

1-71933/MSS (463035-820)  
1059128

Reference No.	Class	Inventors	Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
A	69229	Lei, Sakai, Chama	10057477 01/23/02		Co-owned with MIT; all foreign as will
FP	69229	PC	PCTUS02/03254 01/23/02		PCT
A	69274		06/864,077 05/16/86	4,770,590 09/13/88	
RE	69274		90/086,018 05/21/01	Re-examination of Patent No. 4,770,590	
FA	69274	DI-1	3715601.2 05/09/87	315787 07/06/00	Germany
FA	69274	DI-1	F3745134.0 01/24/96	03/04/99	Germany
FA	69274	FR	8706651 05/15/87	8706851 08/21/92	France
FA	69274	FR-1	8716024 11/19/87	8716024 08/21/92	France
FA	69274	IT	47930A/87 05/14/87	1200283 04/14/89	Italy
FA	69274	JP	62-117197 05/15/87	2681055 08/08/97	Japan
FA	69274	GB	8711230 05/13/87	2190345 08/15/90	Great Britain
FA	69274	GB-1	8922730.0 05/13/87	2223470 08/15/90	Great Britain

F-71935MSS (461055-828)  
1003128

Reference No.		Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
A	69404	MSS	NON-CONTACT CMP MACHINE	60274532 03/08/01	CLOSED PER CLIENT	
F	69447	MSS	SYSTEM AND METHOD TO CONTROL RADIAL DELTA-TIP/er; Stamer	10/095,974 03/08/02		
A	69447	MSS	SYSTEM AND METHOD TO CONTROL RADIAL DELTA TEMPERATURE- -TIP/er; Stamer	PCT/US02/07034 03/08/02		PCI
FF	69447	MSS	SYSTEM AND METHOD TO CONTROL RADIAL DELTA TEMPERATURE- -TIP/er; Stamer	028005953 03/08/02		China
EA	69447	MSS	SYSTEM AND METHOD TO CONTROL RADIAL DELTA TEMPERATURE- -TIP/er; Stamer	2002/572612 03/08/02		Japan
FA	69447	MSS	SYSTEM AND METHOD TO CONTROL RADIAL DELTA TEMPERATURE- -TIP/er; Stamer	2002-7014904 03/08/02		South Korea
FA	69447	MSS	SYSTEM AND METHOD TO CONTROL RADIAL DELTA TEMPERATURE- -TIP/er; Stamer	P20022469 06/28/02		Malaysia
FA	69447	MSS	SYSTEM AND METHOD TO CONTROL RADIAL DELTA TEMPERATURE- -TIP/er; Stamer	200206968-0 03/08/02		Singapore
FE	69447	MSS	SYSTEM AND METHOD TO CONTROL RADIAL DELTA TEMPERATURE- -TIP/er; Stamer	91114419 06/25/02		Taiwan
F	69448	MSS	SYSTEM AND METHOD TO CONTROL RADIAL DELTA TEMPERATURE- -TIP/er; Stamer	02/079649 03/08/02		Europe
A	69448	MSS	INERTIAL TEMPERATURE CONTROL/Stamer	60266526 02/06/01	Closed	
FA	69448	MSS	INERTIAL TEMPERATURE CONTROL/Stamer	10/068,127 02/06/02		
FA	69448	MSS	INERTIAL TEMPERATURE CONTROL/Stamer	021080852 02/06/02		China
FA	69448	MSS	INERTIAL TEMPERATURE CONTROL/Stamer	2002-069336 02/06/02		Japan
FA	69448	MSS	INERTIAL TEMPERATURE CONTROL/Stamer	2002-6778 02/06/02		South Korea
FA	69448	MSS	INERTIAL TEMPERATURE CONTROL/Stamer	P20020366 02/24/02		Malaysia

F-71935/MSS (463035-828)  
1059128



Reference No.		Title/Invention		Serial No./ Filing Date	Pubest No./ Issue Date	Foreign Countries
FA	69448	SG	INERTIAL TEMPERATURE CONTROL/STAINER	200200733-4 02/06/02		Singapore
FA	69448	TW	INERTIAL TEMPERATURE CONTROL/STAINER	91101797 02/01/02	175549 07/07/03	Taiwan
FA	69448	EP	INERTIAL TEMPERATURE CONTROL/STAINER	02250814.7 02/06/02		Europe
A	69477		NON-CONTACT CMP MACHINE/SUB		Closed	
F	69829		APPARATUS FOR THE PREFERENTIAL DEPOSITION OF TEOS+O3 BASED SIOX THIN FILMS ON SILICON SURFACES RELATIVE TO SILICON-NITRIDE SURFACES/Mayer; Ingle; Murphy; Matteson; Kurita	60335,494 11/01/01	Closed	
A	69829		APPARATUS FOR THE PREFERENTIAL DEPOSITION OF TEOS+O3 BASED SIOX THIN FILMS ON SILICON SURFACE RELATIVE TO SILICON-NITRIDE SURFACES/Mayer; Ingle; Murphy; Matteson; Kurita	10285,966 11/01/02		
FA	69829	CN	APPARATUS FOR THE PREFERENTIAL DEPOSITION OF TEOS+O3 BASED SIOX THIN FILMS ON SILICON SURFACES RELATIVE TO SILICON-NITRIDE SURFACES/Mayer; Ingle; Murphy; Matteson; Kurita	11/01/02		China
FA	69829	JP	APPARATUS FOR THE PREFERENTIAL DEPOSITION OF TEOS+O3 BASED SIOX THIN FILMS ON SILICON SURFACES RELATIVE TO SILICON-NITRIDE SURFACES/Mayer; Ingle; Murphy; Matteson; Kurita	2002-320226 11/01/02		Japan
FA	69829	KR	APPARATUS FOR THE PREFERENTIAL DEPOSITION OF TEOS+O3 BASED SIOX THIN FILMS ON SILICON SURFACES RELATIVE TO SILICON-NITRIDE SURFACES/Mayer; Ingle; Murphy; Matteson; Kurita	10/31/02		South Korea
FA	69829	MY	APPARATUS FOR THE PREFERENTIAL DEPOSITION OF TEOS+O3 BASED SIOX THIN FILMS ON SILICON SURFACES RELATIVE TO SILICON-NITRIDE SURFACES/Mayer; Ingle; Murphy; Matteson; Kurita	PI20024020 10/28/02		Malaysia

I-71935/MSS (463035-828)  
1059128

Reference No.	Title/Inventors	Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
EA 69829	APPARATUS FOR THE PREFERENTIAL DEPOSITION OF TEOS+O3 BASED SIOX THIN FILMS ON SILICON SURFACES RELATIVE TO SILICON-NITRIDE SURFACES/Mayer; Inglet; Murphy; Matsson; Kurba	200206357-1 10/28/02		Singapore
EA 69829	APPARATUS FOR THE PREFERENTIAL DEPOSITION OF TEOS+O3 BASED SIOX THIN FILMS ON SILICON SURFACES RELATIVE TO SILICON-NITRIDE SURFACES/Mayer; Inglet; Murphy; Matsson; Kurba	91125270 10/24/02		Taiwan
EA 69829	APPARATUS FOR THE PREFERENTIAL DEPOSITION OF TEOS+O3 BASED SIOX THIN FILMS ON SILICON SURFACES RELATIVE TO SILICON-NITRIDE SURFACES/Mayer; Inglet; Murphy; Matsson; Kurba	02257698.6 01/01/02		Europe
P 70028	MULTILAYER HIGH DIELECTRIC CONSTANT OXIDE FILMS AND METHOD OF MAKING/Senzaki	60/264,428 01/26/01	Closed	
A 70028	MULTILAYER HIGH-k GATE OXIDE THIN FILMS/Senzaki	10/056,625 01/25/02		
P 70292	FLUOROPOLYMER INTERLAYER DIELECTRIC BY CHEMICAL VAPOR DEPOSITION/Mocella; Feiring; Treast; Ertchko; Lopata; Ross	60/288,653 05/04/01	Closed	Application is co-owned with DuPont
	FLUOROPOLYMER INTERLAYER DIELECTRIC BY CHEMICAL VAPOR DEPOSITION/Lopata; Mocella	10/137,875 May 2, 2002		To be filed by DuPont counsel
P 70380	HIGH FLOW RATE BUBBLER WITH A LIQUID PHASE EVAPORATOR/Tookman	60/537,566 11/30/01	Closed	Application is co-owned with DuPont
A 70380	HIGH FLOW RATE BUBBLER WITH A LIQUID PHASE EVAPORATOR/Tookman			To be filed by DuPont counsel
EA 70380	HIGH FLOW RATE BUBBLER SYSTEM AND METHOD/Tookman	11/27/02 FI 20024434 11/27/02		Malaysia

I-7195/MSS (463035-828)  
1099128

Patent No.	Publ. No.	Publ. Date	Publ. No./ Issue Date	Publ. Date	Publ. No./ Issue Date	Foreign Countries
EA 70380	1W	MSS	HIGH FLOW RATE BUBBLER SYSTEM AND METHOD; Tokumasa	91134329		Taiwan
EA 70380	PC	MSS	HIGH FLOW RATE BUBBLER SYSTEM AND METHOD; Tokumasa	112602		PCT
P 70381		MSS WEN	APPARATUS AND METHOD FOR INSULATING A SEAL IN A PROCESS CHAMBER/Draper; Robinson; Lopes	US0238178 11/27/03	Closed	
A 70381		MSS WEN	APPARATUS & METHOD FOR INSULATING A SEAL IN A PROCESS CHAMBER/Draper; Robinson; Lopes	10224687 08/20/02		
EA 70381	CN	MSS	APPARATUS & METHOD FOR INSULATING A SEAL IN A PROCESS CHAMBER/Draper; Robinson; Lopes	02143486.5 08/19/02		China
EA 70381	JP	MSS	APPARATUS & METHOD FOR INSULATING A SEAL IN A PROCESS CHAMBER/Draper; Robinson; Lopes	2002-280066 08/20/02		Japan
EA 70381	KR	MSS	APPARATUS & METHOD FOR INSULATING A SEAL IN A PROCESS CHAMBER/Draper; Robinson; Lopes	2002-0049154 08/20/02		South Korea
EA 70381	MY	MSS	APPARATUS & METHOD FOR INSULATING A SEAL IN A PROCESS CHAMBER/Draper; Robinson; Lopes	08/20/02		Malaysia
EA 70381	SG	MSS	APPARATUS & METHOD FOR INSULATING A SEAL IN A PROCESS CHAMBER/Draper; Robinson; Lopes	P120021060 08/19/02		Singapore
EA 70381	TW	AJT MSS MBG	SYSTEM AND METHOD FOR DEPOSITING INORGANIC/ORGANIC DIELECTRIC FILMS/Draper; Robinson; Lopes	200205046-6 08/20/02		Taiwan
FE 70381	EP	MSS	APPARATUS & METHOD FOR INSULATING A SEAL IN A PROCESS CHAMBER/Draper; Robinson; Lopes	91118697 08/19/02		Europe
A 70466		MSS	CHEMICAL VAPOR DEPOSITION SYSTEM FOR DEPOSITING FLUOROPOLYMER FILMS/Lopata	10253775.5 08/20/02		
P 70524		MSS	MODULAR INJECTOR AND EXHAUST ASSEMBLY/DeDonffy; Mathiesen; Kurita	Closed	Closed	
A 70524		MSS	MODULAR INJECTOR AND EXHAUST ASSEMBLY/DeDonffy; Mathiesen; Kurita	60505406 07/13/01		
EA 70524	CN	MSS TJH MBG	MODULAR INJECTOR AND EXHAUST ASSEMBLY/DeDonffy; Mathiesen; Kurita	10194639 07/13/02		China
			MODULAR INJECTOR/DeDonffy; Mathiesen; Kurita	02141805.5 07/15/02		

E-71935/MSS (463035-828)  
1059128

Reference No.	Title/Abstract	Search No./ Publ. No.	Publ. No./ Exam. No.	Foreign Countries
FA 70524	MODULAR INJECTOR/DeDantley; Mathiesen; Kurita	2602-285716 07/15/02		Japan
EA 70524	MODULAR INJECTOR/DeDantley; Mathiesen; Kurita	2002-0040964 07/13/02		South Korea
EA 70524	MODULAR INJECTOR/DeDantley; Mathiesen; Kurita	P26022836 07/11/02		Malaysia
EA 70524	MODULAR INJECTOR/DeDantley; Mathiesen; Kurita	200204228-1 07/12/02		Singapore
EA 70524	MODULAR INJECTOR/DeDantley; Mathiesen; Kurita	91115568 07/12/02		Taiwan
FE 70524	MODULAR INJECTOR/DeDantley; Mathiesen; Kurita	02254963.8 07/13/02		Europe
A 70824	HEATING SYSTEM AND METHOD FOR HEATING AN ATMOSPHERIC REACTION/Precedent; Seidemann; Kossler	Prepared and Prosecuted by Infineon counsel	This patent appln. is co-owned with Infineon	[related opened countries: Pal. Appl. # MY- 0P120021354; TW-031107447; PC- PCT/EP02/04060]
P 70859	DEPOSITION OF LOW STRESS GERMANIUM AND BORON DOPED SILICA FILMS FOR OPTICAL WAVEGUIDES/Mogstad	60310,026, 08/03/01	Closed	
A 70859	OXIDE STRUCTURE AND METHOD OF FORMING THE OXIDE STRUCTURE/Mogstad	10210,978 08/02/02		China
EA 70859	OXIDE STRUCTURE USEABLE FOR OPTICAL WAVEGUIDE AND METHOD OF FORMING THE OXIDE STRUCTURE/Mogstad	08/08/02		
EA 70859	OXIDE STRUCTURE USEABLE FOR OPTICAL WAVEGUIDE AND METHOD OF FORMING THE OXIDE STRUCTURE/Mogstad	2602-262112 08/05/02		Japan
EA 70859	OXIDE STRUCTURE USEABLE FOR OPTICAL WAVEGUIDE AND METHOD OF FORMING THE OXIDE STRUCTURE/Mogstad	2002-0045980		South Korea

I-71935/MSS (463035-028)  
1039128

Reference No.	Title/Inventors	Essential No./ Filing Date	Patent No./ Issue Date	Foreign Countries
FA 70852	WAVEGUIDE AND METHOD OF FORMING THE OXIDE STRUCTURE/Moggaard	06/03/02		
FA 70859	OXIDE STRUCTURE USABLE FOR OPTICAL WAVEGUIDE AND METHOD OF FORMING THE OXIDE STRUCTURE/Moggaard	FI20022907 08/02/02		Malaysia
FA 70859	OXIDE STRUCTURE USABLE FOR OPTICAL WAVEGUIDE AND METHOD OF FORMING THE OXIDE STRUCTURE/Moggaard	200204671-2 08/02/02		Singapore
FE 70859	OXIDE STRUCTURE USABLE FOR OPTICAL WAVEGUIDE AND METHOD OF FORMING THE OXIDE STRUCTURE/Moggaard	91117477 08/02/02		Taiwan
A 70888	DEPOSITION OF LOW STRESS GERMANIUM AND BORON DOPED SILICA FILMS FOR OPTICAL WAVEGUIDES/Moggaard	02255429.9 08/02/02		Europe
P 70893	BELLOWS ROTARY FEED-THROUGH SEAL/ Ha	Closed		
A 70893	AN IMPROVED DESIGN FOR A LINEAR INJECTOR ASSEMBLY/Mattson; Hakimelahi; Bartholomew; Park; Yuh	60514,762 08/24/01	Closed	
FA 70893	PROTECTIVE SHIELD AND SYSTEM FOR GAS DISTRIBUTION SYSTEM/Mattson; Hakimelahi; Bartholomew; Park; Yuh	10226,459 08/23/02		
FA 70893	DESIGN FOR A LINEAR INJECTOR ASSEMBLY/Mattson; Hakimelahi; Bartholomew; Park; Yuh	PI20023124 08/23/02		Malaysia
FA 70893	DESIGN FOR A LINEAR INJECTOR ASSEMBLY/Mattson; Hakimelahi; Bartholomew; Park; Yuh	91119174 08/23/02		Taiwan
FP 70893	PROTECTIVE SHIELD AND SYSTEM FOR GAS DISTRIBUTION/Mattson; Hakimelahi; Bartholomew; Park; Yuh	PCI/US0227376 08/25/02		PCI
P 70896	ATMOSPHERIC PRESSURE WAFER PROCESSING REACTOR HAVING AN INTERNAL PRESSURE CONTROL SYSTEM AND METHOD/Bartholomew; Bailey; Park; Yuh	60314,760 08/24/01	Closed	
A 70896	ATMOSPHERIC PRESSURE WAFER PROCESSING REACTOR HAVING AN INTERNAL PRESSURE	10226,773 08/23/02		

I-71935/MSS (463035-828)  
1089128

Reference No.	File/Inventors	Control No./ Filing Date	Patent No./ Issue Date	Foreign Countries
FA 70896	MY MSS MRG	CONTROL SYSTEM AND METHOD/Bartholomew; Bailey; Park; Yuh		
FA 70896	TW MSS MBG	ATMOSPHERIC PRESSURE WAFER PROCESSING REACTOR HAVING AN INTERNAL PRESSURE CONTROL SYSTEM AND METHOD/Bartholomew; Bailey; Park; Yuh	P120023123 08/23/02	Malaysia
FP 70896	PC MSS	ATMOSPHERIC PRESSURE WAFER PROCESSING REACTOR HAVING AN INTERNAL PRESSURE CONTROL SYSTEM AND METHOD/Bartholomew; Bailey; Park; Yuh	91119175 08/23/02	Taiwan
P 71033	MSS	ATMOSPHERIC PRESSURE WAFER PROCESSING REACTOR HAVING AN INTERNAL PRESSURE CONTROL SYSTEM AND METHOD/Bartholomew; Bailey; Park; Yuh	FC710302/2/372 08/26/02	PCT
A 71033	MSS	APPARATUS AND PROCESS FOR IMPROVED THIN DIELECTRIC FILMS/Senzaki; Herring; Helms; Osborne SYSTEM AND METHOD FOR IMPROVED THIN DIELECTRIC FILMS/Senzaki; Herring; Helms; Osborne	60/332,397 11/16/01	Closed
FA 71033	CN MSS JW	DIELECTRIC FILMS/Senzaki; Herring; Helms; Osborne SYSTEM AND METHOD FOR IMPROVED THIN DIELECTRIC FILMS/Senzaki; Herring; Helms; Osborne	10/106,677 09/25/02	
FA 71033	JP MSS JW	DIELECTRIC FILMS/Senzaki; Herring; Helms; Osborne SYSTEM AND METHOD FOR IMPROVED THIN DIELECTRIC FILMS/Senzaki; Herring; Helms; Osborne	02157580.0 11/15/02	China
FA 71033	KR MSS JW	SYSTEM AND METHOD FOR IMPROVED THIN DIELECTRIC FILMS/Senzaki; Herring; Helms; Osborne	2002-333209 11/18/02	Japan
FA 71033	MY MSS JW	SYSTEM AND METHOD FOR IMPROVED THIN DIELECTRIC FILMS/Senzaki; Herring; Helms; Osborne	2002-0071019 11/15/02	South Korea
FA 71033	SG MSS JW	SYSTEM AND METHOD FOR IMPROVED THIN DIELECTRIC FILMS/Senzaki; Herring; Helms; Osborne	FI 20024197 11/1/02	Malaysia
FA 71033	TW MSS	SYSTEM AND METHOD FOR IMPROVED THIN DIELECTRIC FILMS/Senzaki; Herring; Helms; Osborne	200204876-5 11/14/02	Singapore
FE 71033	EP MSS JW	SYSTEM AND METHOD FOR IMPROVED THIN DIELECTRIC FILMS/Senzaki; Herring; Helms; Osborne	91133057 11/11/02	Taiwan
		SYSTEM AND METHOD FOR IMPROVED THIN DIELECTRIC FILMS/Senzaki; Herring; Helms; Osborne	02257836.9 11/13/02	Europe

K-71935/MSS (403035-828)  
1059128

Reference No.	IPC Class.	Inventors	Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
A	71023 I	SYSTEM AND METHOD FOR IMPROVED THIN DIELECTRIC FILMS/Senzaki; Herring; Helms; Osborne	Closed		
A	71090	OPTIMIZATION OF CHEMICAL REACTION RATE COEFFICIENTS BY AUTOMATED ITERATIVE COMPUTER SIMULATIONS AND COEFFICIENT VARIATION USING A DESIGNED-EXPERIMENT APPROACH/Chubbant; Bailey	Closed		
P	71181	HEATED VACUUM SUPPORT APPARATUS Tsun, Kana, Jaff Bailey, Sun Kunita, Kris Veock	60533,447 11/26/01	Closed	
A	71181	HEATED VACUUM SUPPORT APPARATUS/Kano; Bailey; Kovsh; Veock	10/303,535 11/22/02		
FA	71181 MY	HEATED VACUUM SUPPORT APPARATUS/Kano; Bailey; Kunita; Veock	PI 20024390 11/25/02		Malaysia
FA	71181 TW	HEATED VACUUM SUPPORT APPARATUS/Kano; Bailey; Kunita; Veock	91134187 11/25/02		Taiwan
FP	71181 PC	HEATED VACUUM SUPPORT APPARATUS/Kano; Bailey; Kunita; Veock	PCT/US02/38106 11/25/02		PCI
P	71197	IN-SITU THERMAL CHAMBER CLEANING/Herring; Sison; Senzaki	60379,381 05/08/02	Closed	
A	71197	SINGLE WAFER THERMAL PROCESSING SYSTEM AND IN-SITU CLEANING METHOD/Herring; Sison; Senzaki	10/518,664 12/12/02		
FA	71197 MY	SINGLE WAFER THERMAL PROCESSING SYSTEM AND IN-SITU CLEANING METHOD/Herring; Sison; Senzaki	PI 20031610 04/29/03		Malaysia
FA	71197 TW	SINGLE WAFER THERMAL PROCESSING SYSTEM AND IN-SITU CLEANING METHOD/Herring; Sison; Senzaki	92110202 04/30/03		Taiwan
FA	71197 PC	SINGLE WAFER THERMAL PROCESSING SYSTEM AND IN-SITU CLEANING METHOD/Herring; Sison; Senzaki	N/A 04/25/03		PCI
A	71355	SEMICONDUCTOR WAFER CARRIER TRANSPORT APPARATUS/Hoyt III; Sauters; Goldman; Mello	06/863,961 05/16/86	4,772,659 02/02/88	

I-71933/MSS (463035-828)  
1089128

Reference No.	Class	Inventors	Filed Date	Publ. No./ Issue Date	Foreign Countries
A	71356	MSS	SEMICONDUCTOR WAFER CARRIER INPUT/ OUTPUT DRAWER/HOIST II; Goldman; Mello	662863,960 05/16/86	
F	71514	MSS	METHOD OF DEPOSITING AN OXIDE FILM BY CHEMICAL VAPOR DEPOSITION TO ACHIEVE COMPLETE GAK-CELL SUB-MICRON STRUCTURES/ Park; Bartholomew; Yuh	60382,780 05/21/02	
A	71514	MSS	METHOD OF DEPOSITING AN OXIDE FILM BY CHEMICAL VAPOR DEPOSITION/ Park; Bartholomew; Yuh	10442,423 05/20/03	
FA	71514 MY	MSS	METHOD OF DEPOSITING AN OXIDE FILM BY CHEMICAL VAPOR DEPOSITION/ Park; Bartholomew; Yuh	PI 20031855 05/20/03	Malaysia
FA	71514 TW	MSS	METHOD OF DEPOSITING AN OXIDE FILM BY CHEMICAL VAPOR DEPOSITION/ Park; Bartholomew; Yuh	05/20/03	Taiwan
FP	71514 FC	MSS	METHOD OF DEPOSITING AN OXIDE FILM BY CHEMICAL VAPOR DEPOSITION/ Park; Bartholomew; Yuh	05/20/03	FCT
P	71564	MSS	SYSTEM AND METHOD FOR HYDROGEN RICH SELECTIVE OXIDATION/Herring; Porter; Dodwell; Nazareno; Radloff; Chatterji	60387,185 06/06/02	
A	71564	MSS	SYSTEM AND METHOD FOR HYDROGEN RICH SELECTIVE OXIDATION/Herring; Porter; Dodwell; Nazareno; Radloff; Chatterji	10456,850 06/06/03	
FA	71564 MY	MSS	SYSTEM AND METHOD FOR HYDROGEN RICH SELECTIVE OXIDATION/Herring; Porter; Dodwell; Nazareno; Radloff; Chatterji	06/06/03	Malaysia
FA	71564 TW	MSS	SYSTEM AND METHOD FOR HYDROGEN RICH SELECTIVE OXIDATION/Herring; Porter; Dodwell; Nazareno; Radloff; Chatterji	06/06/03	Taiwan

I-71933/6-MSS (463 015-426)  
1039126



Reference No.	IPC	Class	Inventors	Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
FP	71564	PC	MSS			
			SYSTEM AND METHOD FOR HYDROGEN RICH SELECTIVE OXIDATION/HERRING; Foster; DeGwell; Nazzari; Radtke; Chatterji	06/06/03		PCT
P	71581		MSS		Closed	
			OZONE OXIDATION OF SILICON SUBSTRATES FOR FORMATION OF AN INTERFACIAL LAYER FOR HIGH-k GATE STACKS/Senzaki; Herring	60/399,463 07/29/02		
A	71581		MSS			Unfiled
			OZONE OXIDATION OF SILICON SUBSTRATES FOR FORMATION OF AN INTERFACIAL LAYER FOR HIGH-k GATE STACKS/Senzaki; Herring			
FP	71581	PC	MSS			
			OZONE OXIDATION OF SILICON SUBSTRATES FOR FORMATION OF AN INTERFACIAL LAYER FOR HIGH-k GATE STACKS/Senzaki; Herring	07/29/03		PCT
FA	71581	TW	MSS			Taiwan
			OZONE OXIDATION OF SILICON SUBSTRATES FOR FORMATION OF AN INTERFACIAL LAYER FOR HIGH-k GATE STACKS/Senzaki; Herring	07/29/03		
P	71582		MSS WEN		Closed	
			OPTIMIZED MINI-BATCH CONFIGURABLE VERTICAL CHAMBER/Qu; Wildman; Collins; Kowalski; Edwards; DuBois; Nam; Torkman; Ma; Starnes	60/396,536 07/15/02		
P	71582	1	MSS WEN		Closed	
			OPTIMIZED MINI-BATCH CONFIGURABLE VERTICAL CHAMBER/Qu; Wildman; Collins; Kowalski; Edwards; DuBois; Nam; Torkman; Ma; Starnes	60/428,526 11/22/02		
P	71606		MSS			
			SYSTEM AND METHOD FOR ATOMIC LAYER DEPOSITION AND REMOVAL/Kaptein; Sang-In Lee	60/391,011 06/23/02		
A	71606		MSS TJH			
			METHOD AND SYSTEM FOR ATOMIC LAYER DEPOSITION/Kaptein; Sang-In Lee			
FA	71606	TW	MSS			Taiwan
			SYSTEM AND METHOD FOR ATOMIC LAYER DEPOSITION AND REMOVAL/Kaptein; Sang-In Lee	06/23/03		
FP	71606	PC	MSS			
			SYSTEM AND METHOD FOR ATOMIC LAYER DEPOSITION AND REMOVAL/Kaptein; Sang-In Lee	PCT/US03/19982 06/23/03		PCT
P	71606	1	MSS		Closed	
			METHOD AND SYSTEM FOR PHOTO-ASSISTED ATOMIC LAYER DEPOSITION AND REMOVAL/ Hochstetler, Jr.; Kaptein; Sang-In Lee; Senzaki	60/391,012 06/23/02		

J-71937/MSS (463035-626)  
1059128

Reference No.	Classification	Inventor	Applicant	Priority Date	Pub. No./Date	Pub. Date	Foreign Countries
71606	I-1W	MSS	METHOD AND SYSTEM FOR PHOTO-ASSISTED ATOMIC LAYER DEPOSITION AND REMOVAL	Hehms, Jr.; Kaphin; Sang-In Lee; Senzaki	06/23/03		Taiwan
71606	I-FC	MSS	METHOD AND SYSTEM FOR PHOTO-ASSISTED ATOMIC LAYER DEPOSITION AND REMOVAL	Hehms, Jr.; Kaphin; Sang-In Lee; Senzaki	06/23/03		PCT
71622		MSS	MOLECULAR LAYER DEPOSITION OF THIN FILMS WITH MIXED COMPONENTS	Senzaki; Sang-In Lee	60/397,629	Closed	
71622		MSS	MOLECULAR LAYER DEPOSITION OF THIN FILMS WITH MIXED COMPONENTS	Senzaki; Sang-In Lee	07/18/02		
71622	TW	MSS	MOLECULAR LAYER DEPOSITION OF THIN FILMS WITH MIXED COMPONENTS	Senzaki; Sang-In Lee	07/16/03		Taiwan
71622	PC	MSS	MOLECULAR LAYER DEPOSITION OF THIN FILMS WITH MIXED COMPONENTS	Senzaki; Sang-In Lee	92119581		PCT
71637		MSS	AFNEXT MACH2 WATER HEATING & TRANSLATE SYSTEM & DESIGN	DeDautney	60/396,735	Closed	
71638		MSS	ATOMIC LAYER DEPOSITION OF HIGH-k DIELECTRIC FILMS	Senzaki; Sang-In Lee	60/396,723	Closed	
71638		MSS	ATOMIC LAYER DEPOSITION OF HIGH-k DIELECTRIC FILMS	Senzaki; Sang-In Lee	07/19/02		
71638	TW	MSS	ATOMIC LAYER DEPOSITION OF HIGH-k DIELECTRIC FILMS	Senzaki; Sang-In Lee	07/17/03		Taiwan
71638	PC	MSS	ATOMIC LAYER DEPOSITION OF HIGH-k DIELECTRIC FILMS	Senzaki; Sang-In Lee	07/19/03		PCT
71639		MSS	LOW TEMPERATURE OZONE ANNEAL OF GATE AND CAPACITOR DIELECTRICS	Senzaki; Sang-In Lee	60/396,742	Closed	
71639	TW	MSS	LOW TEMPERATURE OZONE ANNEAL OF GATE AND CAPACITOR DIELECTRICS	Senzaki; Sang-In Lee	07/19/02		
71639	PCT	MSS	LOW TEMPERATURE OZONE ANNEAL OF GATE AND CAPACITOR DIELECTRICS	Senzaki; Sang-In Lee	07/17/03		Taiwan
71639		MSS	LOW TEMPERATURE OZONE ANNEAL OF GATE AND CAPACITOR DIELECTRICS	Senzaki; Sang-In Lee	07/16/03		PCT

I-71935/MSS (463035-828)  
1059128

Reference No.	Field/Inventor	Abstract No./ Pub. No.	Patent No./ Issue Date	Country
P 71640	MSS	60/396,746 07/19/02	Closed	Taiwan
FA 71640	TW	07/17/03		PCT
FP 71640	PC	60/396,744 07/19/02	Closed	
P 71641	MSS	92119583 07/17/03		Taiwan
A 71641	MSS	07/16/03		PCT
FA 71641	TW	60/396,743 07/19/02	Closed, combined with 71606-1	
FP 71641	PC	60/396,733 07/19/02	Closed	
P 71642	MSS	07/17/03		Taiwan
P 71643	MSS	07/17/03		PCT
FA 71643	TW	07/17/073		Taiwan
FP 71643	PC	07/17/03		PCT

L-71938/MSS (463035-828)  
1059128

Microprocess No.	Class	Inventors	Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries	
F	71644	MSS	IN-SITU FORMATION OF MIM CAPACITORS/Sang-In Lee	60/396,734 07/19/02	Closed	Taiwan
FA	71644	TW	IN-SITU FORMATION OF MIM CAPACITORS/Sang-In Lee	07/17/03		Taiwan
FP	71644	PC	IN-SITU FORMATION OF MIM CAPACITORS/Sang-In Lee	07/17/03		PCI
P	71645	MSS	ATOMIC LAYER DEPOSITION FOR CAPACITOR APPLICATIONS/Sang-In Lee	60/396,743 07/19/02	Closed, combined with 71638	
A	71645	MSS	ATOMIC LAYER DEPOSITION FOR CAPACITOR APPLICATIONS/Sang-In Lee	Closed, combined with 71638		
P	71653	MSS	METHOD OF MAKING METAL CAPS FOR SEMICONDUCTOR DEVICES/Kaplin	60/397,031 07/18/02	Closed	
A	71653	MSS	METHOD OF MAKING METAL CAPS FOR SEMICONDUCTOR DEVICES/Kaplin	N/A		
P	71720	MSS	ATOMIC LAYER DEPOSITION OF HIGH-K METAL OXIDES FOR GATE AND CAPACITOR DIELECTRICS/Sang-In Lee; S.K. Lee; Shin; Senzaki	60/404,372 08/18/02	Closed	
A	71720	MSS	ATOMIC LAYER DEPOSITION OF HIGH-K METAL OXIDES FOR GATE AND CAPACITOR DIELECTRICS/Sang-In Lee; S.K. Lee; Shin; Senzaki			
FA	71720	TW	ATOMIC LAYER DEPOSITION OF HIGH-K METAL OXIDES FOR GATE AND CAPACITOR DIELECTRICS/Sang-In Lee; S.K. Lee; Shin; Senzaki	08/14/03		Taiwan
FP	71720	PC	ATOMIC LAYER DEPOSITION OF HIGH-K METAL OXIDES FOR GATE AND CAPACITOR DIELECTRICS/Sang-In Lee; S.K. Lee; Shin; Senzaki	08/18/03		PCI
P	71721	MSS	ATOMIC LAYER DEPOSITION OF METAL SILICATES FOR HIGH-K GATE AND CAPACITOR DIELECTRICS/Sang-In Lee; S.K. Lee; Shin; Senzaki	60/404,371 08/18/02	Closed	

E-71935/MSS (463035-828)  
1039128

Index No.	Pub. No.	Title/Inventors	Search No./ Filing Date	Patent No./ Issue Date	Foreign Countries
A	71721	ATOMIC LAYER DEPOSITION OF METAL SILICATES FOR HIGH-K GATE AND CAPACITOR DIELECTRICS/Sang-In Lee; S.K. Lee; Shim; Senzaki			
FA	71721	ATOMIC LAYER DEPOSITION OF METAL SILICATES FOR HIGH-K GATE AND CAPACITOR DIELECTRICS/Sang-In Lee; S.K. Lee; Shim; Senzaki	08/14/03		Taiwan
FP	71721	ATOMIC LAYER DEPOSITION OF METAL SILICATES FOR HIGH-K GATE AND CAPACITOR DIELECTRICS/Sang-In Lee; S.K. Lee; Shim; Senzaki	08/18/03		PCI
P	71722	LOW TEMPERATURE DEPOSITION OF SILICON OXIDES AND SILICON OXYNITRIDE/Sang-In Lee; S.K. Lee; Shim; Senzaki	60/404,363 08/18/02	Closed	
A	71722	LOW TEMPERATURE DEPOSITION OF SILICON OXIDES AND SILICON OXYNITRIDE/Sang-In Lee; S.K. Lee; Shim; Senzaki			
FA	71722	LOW TEMPERATURE DEPOSITION OF SILICON OXIDES AND SILICON OXYNITRIDE/Sang-In Lee; S.K. Lee; Shim; Senzaki	08/14/03		Taiwan
FP	71722	LOW TEMPERATURE DEPOSITION OF SILICON OXIDES AND SILICON OXYNITRIDE/Sang-In Lee; S.K. Lee; Shim; Senzaki	08/18/03		PCI
P	71730	LOW TEMPERATURE DEPOSITION OF SILICON BASED THIN FILMS BY SINGLE WAFER HOT-WALL RAPID THERMAL CHEMICAL VAPOR DEPOSITION (RTCVD)/Senzaki; Barelli; Teasdale;	60/408,709 09/05/02	Closed	
A	71730	LOW TEMPERATURE DEPOSITION OF SILICON BASED THIN FILMS BY SINGLE WAFER HOT-WALL RAPID THERMAL CHEMICAL VAPOR DEPOSITION (RTCVD)/Senzaki; Barelli; Teasdale;	09/05/03		
P	71730	LOW TEMPERATURE DEPOSITION OF SILICON BASED THIN FILMS BY SINGLE WAFER HOT-WALL RAPID THERMAL CHEMICAL VAPOR DEPOSITION (RTCVD)/Senzaki; Barelli; Teasdale;	Closed, combined with 71730		

F-71935/MSS (461035-828)  
1039128

Reference No.	Classification	Inventors	Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
F 71731	B3IS TJH	Sequential two-step atomic layer deposition of copper seed layer/Suzuki	60419,633 10/17/02		
A 71731	MSS	Sequential two-step atomic layer deposition of copper seed layer/Suzuki			Client Ref. # D- 7006
A 71732	MSS	Two-step sequential growth of high-k gate dielectrics by atomic layer deposition/Suzuki			Client Ref. # D- 7005
A 71733	MSS TJH	Anneal process for silicon nitride dielectric thin films/Suzuki; Hutchko			Client Ref. D-7007
A 71748	MSS WEN	Thermal processing system and configurable vertical chamber/DuBois; Nann			
FA 71748	TW	Thermal processing system and configurable vertical chamber/DuBois; Nann			
FP 71748	PC	Thermal processing system and configurable vertical chamber/DuBois; Nann; Wildman; Qui; Kowalaki	07/10/03		Taiwan
A 71749	MSS TJH	Thermal processing system and configurable vertical chamber/DuBois; Nann; Wildman; Qui; Kowalaki	07/10/03		PCI
A 71750	MSS TJH	Fedestal thermal shield/Wildman; Qui	Closed, combined with 71748		
FA 71750	TW	Thermal processing apparatus and method of backfilling a chamber cleaning/Torkaman			Taiwan
FP 71750	CT	Thermal processing apparatus and method of backfilling a chamber cleaning/Torkaman	07/10/03		
A 71751	MSS TJH	Thermal processing apparatus and method of backfilling a chamber cleaning/Torkaman vacuum assembly with multi-stage valve sequence/Qui	07/10/03		PCI

I-71935/MSS (463035-828)  
1039128

Reference No.		Title/Inventor		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Country
FA	71751	TW	MSS	VACUUM ASSEMBLY WITH MULTI-STAGE VALVE SEQUENCE/Qu	07/10/03	Taiwan
FP	71751	PC	MSS	VACUUM ASSEMBLY WITH MULTI-STAGE VALVE SEQUENCE/Qu	07/10/03	PCT
A	71752		MSS WEN	CYCLONIC COOLING SYSTEM AND METHOD/Qu; Collins		
FA	71752	TW	MSS	CYCLONIC COOLING SYSTEM AND METHOD/Qu; Collins	07/10/03	Taiwan
FP	71752	PC	MSS	CYCLONIC COOLING SYSTEM AND METHOD/Qu; Collins	07/10/03	PCT
A	71753		MSS WEN	COOLING SYSTEM AND METHOD/Qu; Collins	Closed, combined with 71752	
A	71754		MSS	FEED FORWARD TEMPERATURE CONTROLLER/MS	Closed	
A	71755		MSS KRG	ALIGNMENT APPARATUS AND METHOD OF ALIGNING A WAFER/MS	out hold	
A	71756		MSS	COMMUNICATION PROTOCOL AND METHOD OF IMPROVED ROBOT THROUGHPUT/MS		
A	71757		MSS	DISTRIBUTED SINGLE WIRE NETWORKING ELEVATOR CONTROL SYSTEM AND METHOD/MS		
FA	71757	TW	MSS	SERVOMOTOR CONTROL SYSTEM & METHOD IN A SEMICONDUCTOR MANUFACTURING ENVIRONMENT; John M.	07/10/03	Taiwan
FP	71757	PC	MSS	SERVOMOTOR CONTROL SYSTEM & METHOD IN A SEMICONDUCTOR MANUFACTURING ENVIRONMENT; John M.	07/10/03	PCT
A	71758		MSS KRG	LOAD PORT; Jeffrey E. Kowalski		
FA	71758	TW	MSS	LOAD PORT APPARATUS; Jeffrey E. Kowalski	07/15/03	Taiwan

I-71935/MSS (461035-826)  
1039128

Reference No.		Title/Inventors		Serial No./ Publ. Date	Patent No./ Issued Date	Foreign Countries
FP	71758	PC	LOAD POKI APPARATUS; Jeffrey E. Kowalski	07/15/03		PCT
A	71759		THERMAL PROCESSING CHAMBER ENVIRONMENTAL CONTROL SYSTEM AND METHOD; Alan Stamer			
FA	71759	TW	CONTROL OF A GASEOUS ENVIRONMENT IN A WAFER LOADING CHAMBER; Alan Stamer	07/15/03		Taiwan
FP	71759	PC	CONTROL OF A GASEOUS ENVIRONMENT IN A WAFER LOADING CHAMBER; Alan Stamer	07/15/03		PCT
A	71768		METHOD AND SYSTEM FOR ISOTHERMAL HEATING OF WAFERS; Jeffrey Kowalski	Closed, combined with 71748		
A	71795		HEATER ELEMENT SELECTABLE FOR VARIABLE TEMPERATURE PROCESSING/Qtd			
FA	71795	TW	VARIABLE HEATER ELEMENT FOR LOW TO HIGH TEMPERATURE RANGES/Qtd	07/10/03		Taiwan
FP	71795	PC	VARIABLE HEATER ELEMENT FOR LOW TO HIGH TEMPERATURE RANGES/Qtd	07/10/03		PCT
A	71796		T-RAIL SUPPORT/DuBois			
FA	71796	TW	METHOD & APPARATUS FOR SUPPORTING SEMICONDUCTOR WAFERS/DuBois	07/10/03		Taiwan
FP	71796	PC	METHOD & APPARATUS FOR SUPPORTING SEMICONDUCTOR WAFERS/DuBois	07/10/03		PCT
A	71797		FIBER FORWARD CONTROL SYSTEM AND METHOD/Teckman; Radlit (This case may be related to A-71754)			
A	71798		SYSTEM ARCHITECTURE AND METHOD FOR SEMICONDUCTOR FABRICATION/Helwig; Wlozen			

E-71935/MSS (463035-828)  
1029128



Reference No.	Classification	Inventors	Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
P	MSS TUE	71824 REMOTE PLASMA NITRATION OF HIGH-K GATE DIELECTRICS/Senzaki; Bercaw; Chatham; Higuchi; Lopez	60/424,891 11/08/02		
A	MSS	71824 REMOTE PLASMA NITRATION OF HIGH-K GATE DIELECTRICS/Senzaki; Bercaw; Chatham; Higuchi; Lopez			
A	MSS TUE	71824 METHOD OF ATOMIC LAYER REMOVAL OR BLEACHING/Sang-in Lee	Closed, combined with 71696		
P	MSS	72081 TRANSPORT SYSTEM HAVING SHARED LOAD-LOCK FRONT-END ASSEMBLY FOR TRANSFER OF MEDIA IN A CONTROLLED ENVIRONMENT	60/443,969 01/31/03		
P	MSS	72138 ELECTRODE STRUCTURE AND METHOD OF FABRICATING AN ELECTRODE HAVING LOW TEMPERATURE OXIDE FILM; S.I. Lee, Y. Senzaki			Client Ref. No. -- D-7031
P	MSS	72218 METHOD OF FABRICATING MULTI-COMPONENT FILMS; Y. Senzaki, S.G. Park	60/464,438 04/21/03		Client Ref. No. -- D-2419
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